

=> s Yitzchaik, Shlomo/in

L1 4 YITZCHAIK, SHLOMO/IN

=> d 11 1-4

L1 ANSWER 1 OF 4 USPATFULL
 AN 2000:27670 USPATFULL
 TI Self-assembled superlattices and waveguides prepared for use therewith
 IN **Yitzchaik, Shlomo**, Evanston, IL, United States
 Lundquist, Paul M., Bloomington, MN, United States
 Marks, Tobin J., Evanston, IL, United States
 PA Northwestern University, Evanston, IL, United States (U.S. corporation)
 PI US 6033774 20000307
 AI US 1997-857769 19970515 (8)
 RLI Continuation of Ser. No. US 1994-355639, filed on 14 Dec 1994, now
 abandoned
 DT Utility
 LN.CNT 854
 INCL INCLM: 428/333.000
 INCLS: 252/582.000; 359/328.000; 359/329.000; 359/330.000; 359/332.000;
 385/122.000; 385/129.000; 385/130.000; 385/131.000; 428/429.000;
 428/451.000
 NCL NCLM: 428/333.000
 NCLS: 252/582.000; 359/328.000; 359/329.000; 359/330.000; 359/332.000;
 385/122.000; 385/129.000; 385/130.000; 385/131.000; 428/429.000;
 428/451.000
 IC [7]
 ICM: B32B009-04
 EXF 252/582; 359/328; 359/329; 359/330; 359/332; 385/122; 385/129; 385/130;
 385/131; 428/333; 428/336; 428/405; 428/429; 428/447; 428/451
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L1 ANSWER 2 OF 4 USPATFULL
 AN 95:108285 USPATFULL
 TI Photochromic spirooxazine monomers and polysiloxanes
 IN Krongauz, Valeri, Rehovot, Israel
 Buchhultz, Frida, Rishon Lezion, Israel
 Zelichenok, Alexander, Rehovot, Israel
Yitzchaik, Shlomo, Evanston, IL, United States
 PA Yeda Research and Development Co. Ltd. at the Weizmann Institute of
 Science, Tel Aviv, Israel (non-U.S. corporation)
 PI US 5473068 19951205
 AI US 1994-197967 19940217 (8)
 RLI Division of Ser. No. US 1993-19765, filed on 19 Feb 1993, now patented,
 Pat. No. US 5322945
 DT Utility
 LN.CNT 652
 INCL INCLM: 544/075.000
 INCLS: 544/069.000
 NCL NCLM: 544/071.000
 NCLS: 544/069.000
 IC [6]

ICM: C07D498-20
EXF 544/71; 544/69
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L1 ANSWER 3 OF 4 USPATFULL
AN 95:65463 USPATFULL
TI Method and system for producing second order nonlinear optical effects
using in-plane poled polymer films
IN Berkovic, Garry, Rehovot, Israel
Krongauz, Valeri, Rehovot, Israel
Yitzchaik, Schlomo, Rehovot, Israel
Yitzchaik, Shlomo, Holon, Israel
PA Yeda Research and Development Co., Ltd., Rehovot, Israel (non-U.S.
corporation)
PI US 5434699 19950718
AI US 1994-214652 19940317 (8)
RLI Continuation-in-part of Ser. No. US 1993-149395, filed on 9 Nov 1993,
now abandoned which is a continuation of Ser. No. US 1991-644371, filed
on 23 Jan 1991, now patented, Pat. No. US 5262890
DT Utility
LN.CNT 1193
INCL INCLM: 359/328.000
NCL NCLM: 359/328.000
IC [6]
ICM: G02F001-37
EXF 359/328

L1 ANSWER 4 OF 4 USPATFULL
AN 94:53545 USPATFULL
TI Photochromic spirooxazine monomers and polysiloxanes
IN Krongauz, Valeri, Rehovot, Israel
Buchhultz, Frida, Rishon Lezion, Israel
Zelichenok, Alexander, Rehovot, Israel
Yitzchaik, Shlomo, Evanston, IL, United States
PA Yeda Research and Development Co. Ltd., Rehovot, Israel (non-U.S.
corporation)
PI US 5322945 19940621
AI US 1993-19765 19930219 (8)
DT Utility
LN.CNT 691
INCL INCLM: 544/069.000
INCLS: 544/071.000; 252/586.000; 351/163.000; 430/345.000; 359/241.000;
359/642.000
NCL NCLM: 544/069.000
NCLS: 252/586.000; 351/163.000; 359/241.000; 359/642.000; 430/345.000;
544/071.000
IC [5]
ICM: C07F007-08
ICS: C07F007-10; C07F007-18
EXF 544/69; 544/71; 252/586; 351/163; 350/409; 350/354; 430/345
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> s epitaxy

L2 9483 EPITAXY

=> s ?molecular layer?

300982 ?MOLECULAR
677794 LAYER?
L3 2933 ?MOLECULAR LAYER?
(?MOLECULAR (W) LAYER?)

=> s 12 and 13

L4 171 L2 AND L3

=> s 14 and z axis

245850 Z
759154 AXIS
22121 Z AXIS
(Z(W)AXIS)

L5 3 L4 AND Z AXIS

=> s 15 and dianhydride#

6695 DIANHYDRIDE#
L6 0 L5 AND DIANHYDRIDE#

=> d 15 1-3

L5 ANSWER 1 OF 3 USPATFULL
AN 1998:116796 USPATFULL
TI Maintaining interatomic distance between an STM probe and a recording layer
IN Nose, Hiroyasu, Zama, Japan
Kawase, Toshimitsu, Atsugi, Japan
Yamano, Akihiko, Yokohama, Japan
PA Canon Kabushiki Kaisha, Tokyo, Japan (non-U.S. corporation)
PI US 5812516 19980922
AI US 4754654 19950607 (8)
RLI Division of Ser. No. 465908, filed on 6 Jun 1995, now abandoned
which is a continuation of Ser. No. 800716, filed on 3 Dec 1991, now abandoned which is a continuation of Ser. No. 326677, filed on 21 Mar 1989, now abandoned
PRAI JP 1963-71036 19880325
DT Utility
LN.CNT 942
INCL INCLM: 369/126.000
INCLS: 250/306.000
NCL NCLM: 369/126.000
NCLS: 250/306.000
IC [6]
ICM: G11B009-00
ICS: G06K017-00
EXF 369/126; 369/101; 369/124; 369/112; 250/306; 250/307; 365/151; 365/128

L5 ANSWER 2 OF 3 USPATFULL
AN 97:22626 USPATFULL
TI Method for arranging a polynucleotide on a substrate for point-by-point analysis of the bases thereof
IN Fourmentin-Guilbert, Jean E. R., 84, avenue de la Republique, 93160 Noisy Le Grand, France
PI US 5612181 19970318
AI US 1994-282627 19940729 (8)
RLI Continuation-in-part of Ser. No. US 1992-845918, filed on 4 Mar 1992, now abandoned which is a continuation-in-part of Ser. No. US 1990-541530, filed on 21 Jun 1990, now abandoned
PRAI FR 1989-8284 19890621
DT Utility
LN.CNT 714

INCL INCLM: 435/006.000
INCLS: 536/025.400
NCL NCLM: 435/006.000
NCLS: 536/025.400
IC [6]
ICM: C12Q001-68
ICS: G01N033-24
EXF 435/6; 536/25.4
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 3 OF 3 USPATFULL
AN 95:67455 USPATFULL
TI Ordered mixed crystal semiconductor superlattice device
IN Nakata, Yoshiaki, Kawasaki, Japan
Ueda, Osamu, Kawasaki, Japan
Nakamura, Satoshi, Kawasaki, Japan
PA Fujitsu Limited, Kawasaki, Japan (non-U.S. corporation)
PI US 5436468 19950725
AI US 1994-308217 19940919 (8)
RLI Continuation of Ser. No. US 1993-31850, filed on 16 Mar 1993, now
abandoned
PRAI JP 1992-60167 19920317
JP 1992-223793 19920824
JP 1992-271969 19921009
DT Utility
LN.CNT 1518
INCL INCLM: 257/015.000
INCLS: 257/014.000; 257/022.000; 257/628.000
NCL NCLM: 257/015.000
NCLS: 257/014.000; 257/022.000; 257/628.000
IC [6]
ICM: H01L029-04
ICS: H01L029-161
EXF 257/15; 257/17; 257/20; 257/21; 257/22; 257/24; 257/194; 257/201;
257/628
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> s 14 and dianhydride#

6695 DIANHYDRIDE#
L7 13 L4 AND DIANHYDRIDE#

=> d 17 1-13

L7 ANSWER 1 OF 13 USPATFULL
AN 1999:73668 USPATFULL
TI Optical circuit device, its manufacturing process and a multilayer
optical circuit using said optical circuit device
IN Yoshimura, Tetsuzo, Kawasaki, Japan
Tatsuura, Satoshi, Kawasaki, Japan
Sotoyama, Wataru, Kawasaki, Japan
Yoneda, Yasuhiro, Kawasaki, Japan
Motoyoshi, Katsusada, Kawasaki, Japan
Tsukamoto, Koji, Kawasaki, Japan
Ishitsuka, Takeshi, Kawasaki, Japan
PA Fujitsu Limited, Kanagawa, Japan (non-U.S. corporation)
PI US 5917980 19990629
AI US 1993-28550 19930308 (8)
PRAI JP 1992-48961 19920306
JP 1992-52206 19920311
JP 1992-159350 19920618

JP 1992-179909 19920707
 JP 1992-189554 19920716
 DT Utility
 LN.CNT 1693
 INCL INCLM: 385/129.000
 INCLS: 385/014.000; 385/130.000; 385/131.000; 385/132.000; 385/141.000;
 385/122.000; 385/041.000
 NCL NCLM: 385/129.000
 NCLS: 385/014.000; 385/041.000; 385/122.000; 385/130.000; 385/131.000;
 385/132.000; 385/141.000
 IC [6]
 ICM: G02B006-10
 EXF 385/2; 385/5; 385/7; 385/8; 385/9; 385/11; 385/14; 385/16; 385/24;
 385/27; 385/40; 385/41; 385/43; 385/129; 385/130; 385/131; 385/132;
 385/141; 385/142; 385/143; 385/145; 385/122; 359/1; 359/15; 359/22;
 359/27; 359/34; 359/35
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 2 OF 13 USPATFULL
 AN 1999:27356 USPATFULL
 TI Photosensitive material and process for the preparation thereof
 IN Takimoto, Akio, Neyagawa, Japan
 Wakemoto, Hirofumi, Neyagawa, Japan
 Tanaka, Eiichiro, Kishiwada, Japan
 Watanabe, Masanori, Katano, Japan
 Asayama, Junko, Suita, Japan
 Ogawa, Hisahito, Ikoma-gun, Japan
 Sato, Shigehiro, Osaka, Japan
 Yokotani, Fumiko, Suita, Japan
 PA Matsushita Electric Industrial Co., Ltd., Osaka-fu, Japan (non-U.S.
 corporation)
 PI US 5876891 19990302
 AI US 1995-450909 19950526 (8)
 RLI Division of Ser. No. US 1993-90638, filed on 13 Jul 1993, now patented,
 Pat. No. US 5486442 which is a continuation-in-part of Ser. No. US
 1991-673759, filed on 25 Mar 1991, now abandoned
 PRAI JP 1990-73777 19900323
 JP 1990-73778 19900323
 JP 1990-73779 19900323
 JP 1990-74971 19900325
 JP 1990-335910 19901129
 DT Utility
 LN.CNT 1862
 INCL INCLM: 430/071.000
 INCLS: 430/072.000; 430/078.000; 430/096.000; 430/135.000
 NCL NCLM: 430/071.000
 NCLS: 430/072.000; 430/078.000; 430/096.000; 430/135.000
 IC [6]
 ICM: G03G005-00
 ICS: G03G015-06
 EXF 430/78; 430/96; 430/135; 430/71; 430/72
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 3 OF 13 USPATFULL
 AN 97:68533 USPATFULL
 TI Organic polymer and preparation and use thereof
 IN Takimoto, Akio, Neyagawa, Japan
 Wakemoto, Hirofumi, Neyagawa, Japan
 Tanaka, Eiichiro, Kishiwada, Japan
 Watanabe, Masanori, Katano, Japan
 Asayama, Junko, Suita, Japan
 Ogawa, Hisahito, Ikoma-gun, Japan
 Sato, Shigehiro, Osaka, Japan

Yokotani, Fumiko, Suita, Japan
PA Matsushita Electric Industrial Co., Ltd., Osaka, Japan (non-U.S. corporation)
PI US 5654367 19970805
AI US 1995-453061 19950526 (8)
RLI Division of Ser. No. US 1993-90638, filed on 13 Jul 1993, now patented, Pat. No. US 5486442 which is a continuation of Ser. No. US 1991-673759, filed on 25 Mar 1991, now abandoned
PRAI JP 1990-73777 19900323
JP 1990-73778 19900323
JP 1990-73779 19900323
JP 1990-74971 19900325
JP 1990-335910 19901129
DT Utility
LN.CNT 1848
INCL INCLM: 525/178.000
INCLS: 525/180.000; 525/181.000; 528/288.000; 528/290.000; 528/295.000; 528/422.000; 528/425.000
NCL NCLM: 525/178.000
NCLS: 525/180.000; 525/181.000; 528/288.000; 528/290.000; 528/295.000; 528/422.000; 528/425.000
IC [6]
ICM: C08F008-30
ICS: C08L077-00
EXF 525/178; 525/180; 525/181; 528/272; 528/288; 528/290; 528/295; 528/422; 528/425
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 4 OF 13 USPATFULL
AN 97:7990 USPATFULL
TI Organic polymer and preparation and use thereof
IN Takimoto, Akio, Neyagawa, Japan
Wakemoto, Hirofumi, Neyagawa, Japan
Tanaka, Eiichiro, Kishiwada, Japan
Watanabe, Masanori, Katano, Japan
Asayama, Junko, Suita, Japan
Ogawa, Hisahito, Ikoma-gun, Japan
Sato, Shigehiro, Osaka, Japan
Yokotani, Fumiko, Suita, Japan
PA Matsushita Electric Industrial Co., Ltd., Osaka-fu, Japan (non-U.S. corporation)
PI US 5597889 19970128
AI US 1995-451727 19950526 (8)
RLI Division of Ser. No. US 1993-90638, filed on 13 Jul 1993, now patented, Pat. No. US 5486442 which is a continuation of Ser. No. US 1991-673759, filed on 25 Mar 1991, now abandoned
PRAI JP 1990-73777 19900323
JP 1990-73778 19900323
JP 1990-73779 19900323
JP 1990-74971 19900325
JP 1990-335910 19901129
DT Utility
LN.CNT 1872
INCL INCLM: 528/353.000
INCLS: 528/125.000; 528/126.000; 528/128.000; 528/170.000; 528/172.000; 528/176.000; 528/183.000; 528/185.000; 528/187.000; 528/188.000; 528/220.000; 528/229.000; 428/001.000; 428/473.500
NCL NCLM: 427/058.000
NCLS: 428/001.260; 428/473.500; 528/125.000; 528/126.000; 528/128.000; 528/170.000; 528/172.000; 528/176.000; 528/183.000; 528/185.000; 528/187.000; 528/188.000; 528/220.000; 528/229.000; 528/353.000
IC [6]
ICM: C08G069-26

ICS: C09K019-00
EXF 528/353; 528/125; 528/126; 528/128; 528/170; 528/172; 528/176; 528/183;
528/185; 528/187; 528/188; 528/220; 528/229; 428/1; 428/473.5
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 5 OF 13 USPATFULL
AN 96:7632 USPATFULL
TI Organic polymer and preparation and use in crystal spatial light
modulator
IN Takimoto, Akio, Neyagawa, Japan
Wakemoto, Hirofumi, Neyagawa, Japan
Tanaka, Eiichiro, Kishiwada, Japan
Watanabe, Masanori, Katano, Japan
Asayama, Junko, Suita, Japan
Ogawa, Hisahito, Ikoma, Japan
Sato, Shigehiro, Osaka, Japan
Yokotani, Fumiko, Suita, Japan
PA Matsushita Electric Industrial Co., Ltd., Osaka, Japan (non-U.S.
corporation)
PI US 5486442 19960123
AI US 1993-90638 19930713 (8)
RLI Continuation of Ser. No. US 1991-673759, filed on 25 Mar 1991, now
abandoned
PRAI JP 1990-73777 19900323
JP 1990-73778 19900323
JP 1990-73779 19900323
JP 1990-74971 19900325
JP 1990-335910 19901129
DT Utility
LN.CNT 1852
INCL INCLM: 430/078.000
INCLS: 430/014.000; 430/325.000; 359/067.000; 359/071.000; 359/072.000;
522/148.000; 522/164.000
NCL NCLM: 430/078.000
NCLS: 349/114.000; 349/116.000; 430/325.000; 522/148.000; 522/164.000
IC [6]
ICM: G03G005-00
EXF 430/78; 430/220; 430/325; 359/67; 359/71; 359/72; 522/148; 522/164;
522/904; 522/905
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 6 OF 13 USPATFULL
AN 95:76714 USPATFULL
TI Organic functional optical thin film, fabrication and use thereof
IN Yoshimura, Tetsuzo, Kawasaki, Japan
Yano, Ei, Kawasaki, Japan
Tatsuura, Satoshi, Kawasaki, Japan
Sotoyama, Wataru, Kawasaki, Japan
PA Fujitsu Limited, Kawasaki, Japan (non-U.S. corporation)
PI US 5444811 19950822
AI US 1992-858074 19920326 (7)
PRAI JP 1991-132448 19910326
JP 1991-239559 19910919
DT Utility
LN.CNT 2877
INCL INCLM: 385/141.000
INCLS: 385/129.000; 385/130.000; 385/131.000; 385/122.000; 385/143.000;
385/145.000; 427/162.000; 427/163.200; 427/166.000; 427/167.000
NCL NCLM: 385/141.000
NCLS: 385/122.000; 385/129.000; 385/130.000; 385/131.000; 385/143.000;
385/145.000; 427/162.000; 427/163.200; 427/166.000; 427/167.000
IC [6]
ICM: G02B006-12

ICS: B05D005-06
EXF 385/123; 385/122; 385/128; 385/129; 385/130; 385/131; 385/141; 385/143;
385/145; 385/14; 359/321; 359/326; 359/332; 427/162; 427/164; 427/166;
427/167; 427/248.1; 427/255.6; 427/269; 427/407.1; 427/410; 427/412.4;
427/163.2

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 7 OF 13 USPATFULL
AN 94:91511 USPATFULL
TI Liquid crystal display devices with organic thin film formed by
compressing molecules on liquid surface and transferring to substrate
by
horizontal lifting
IN Imazeki, Shuji, Saitama, Japan
Tomiooka, Yasushi, Saitama, Japan
Tanaka, Naoki, Saitama, Japan
Taniguchi, Yoshio, Hino, Japan
Kawakami, Hideaki, Chiba, Japan
Kondo, Katsumi, Katsuta, Japan
Yamasaki, Masami, Saitama, Japan
PA Hitachi, Ltd., Tokyo, Japan (non-U.S. corporation)
PI US 5357357 19941018
AI US 1990-584971 19900919 (7)
PRAI JP 1989-1241975 19890920
JP 1989-1241990 19890920
JP 1989-1246289 19890925
DT Utility
LN.CNT 1588
INCL INCLM: 359/076.000
INCLS: 359/063.000; 359/075.000; 428/001.000
NCL NCLM: 428/001.310
NCLS: 349/095.000; 349/096.000; 349/123.000; 349/132.000
IC [5]
ICM: G02F001-1337
ICS: G02F001-1335; C09K019-00
EXF 359/75; 359/63; 359/76; 359/87; 428/1
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 8 OF 13 USPATFULL
AN 93:65916 USPATFULL
TI Polarizer with patterned diacetylene layer, method for producing the
same, and liquid crystal display device including such polarizer
IN Imazeki, Shuji, Saitama, Japan
Tomiooka, Yasushi, Saitama, Japan
Tanaka, Naoki, Saitama, Japan
Kanetake, Tatsuo, Saitama, Japan
Kondo, Seiichi, Saitama, Japan
Taniguchi, Yoshio, Hino, Japan
Kondo, Katsumi, Katsuta, Japan
Kawakami, Hideaki, Chiba, Japan
PA Hitachi, Ltd., Tokyo, Japan (non-U.S. corporation)
PI US 5235449 19930810
AI US 1991-662642 19910301 (7)
RLI Continuation-in-part of Ser. No. US 1990-584971, filed on 19 Sep 1990
PRAI JP 1990-49347 19900302
DT Utility
LN.CNT 789
INCL INCLM: 359/063.000
INCLS: 359/485.000; 359/492.000; 359/500.000
NCL NCLM: 349/096.000
NCLS: 359/485.000; 359/492.000; 359/500.000
IC [5]
ICM: G02F001-1335

ICS: G02B005-30
EXF 359/63; 359/64; 359/485; 359/492; 359/500
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 9 OF 13 USPATFULL
AN 92:85320 USPATFULL
TI Organic thin film element
IN Nakayama, Toshio, Fujisawa, Japan
Gemma, Nobuhiro, Yokohama, Japan
Miura, Akira, Toride, Japan
Naito, Katsuyuki, Yokohama, Japan
Egusa, Syun, Yokohama, Japan
PA Kabushiki Kaisha Toshiba, Kawasaki, Japan (non-U.S. corporation)
PI US 5155566 19921013
AI US 1991-675964 19910327 (7)
PRAI JP 1990-75413 19900327
DT Utility
LN.CNT 1029
INCL INCLM: 357/030.000
INCLS: 357/008.000
NCL NCLM: 257/040.000
NCLS: 257/103.000; 257/443.000
IC [5]
ICM: H01L027-14
ICS: H01L031-00
EXF 357/30R; 357/8
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 10 OF 13 USPATFULL
AN 91:100776 USPATFULL
TI Electric-electronic device including polyimide thin film
IN Uekita, Masakazu, Hyogo, Japan
Awaji, Hiroshi, Hyogo, Japan
PA Kanegafuchi Kagaku Kogyo Kabushiki Kaisha, Osaka, Japan (non-U.S. corporation)
PI US 5072262 19911210
AI US 1989-418618 19891010 (7)
RLI Continuation of Ser. No. US 1987-24421, filed on 10 Mar 1987, now abandoned
PRAI JP 1986-54080 19860311
DT Utility
LN.CNT 1093
INCL INCLM: 357/006.000
INCLS: 357/023.150
NCL NCLM: 257/410.000
NCLS: 257/643.000
IC [5]
ICM: H01L049-02
EXF 357/6; 357/8; 357/23.1; 357/23.15
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 11 OF 13 USPATFULL
AN 91:100248 USPATFULL
TI Patterned thin film and process for preparing the same
IN Uekita, Masakazu, Kobe, Japan
Awaji, Hiroshi, Kobe, Japan
Murata, Makoto, Kobe, Japan
Mizunuma, Satoshi, Kobe, Japan
PA Kanegafuchi Kagaku Kogyo Kabushiki Kaisha, Osaka, Japan (non-U.S. corporation)
PI US 5071733 19911210
AI US 1989-459153 19891229 (7)
RLI Division of Ser. No. US 1988-248683, filed on 23 Sep 1988, now patented,

Pat. No. US 4943471 which is a continuation-in-part of Ser. No. US 1987-51350, filed on 19 May 1987, now patented, Pat. No. US 4839219

PRAI JP 1986-116390 19860520
JP 1986-116391 19860520
JP 1987-241640 19870925
JP 1988-106048 19880428

DT Utility
LN.CNT 918
INCL INCLM: 430/326.000
INCLS: 430/330.000; 430/270.000
NCL NCLM: 430/326.000
NCLS: 430/270.100; 430/330.000
IC [5]
ICM: G03F007-039
EXF 430/326; 430/270; 430/330
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 12 OF 13 USPATFULL
AN 90:57699 USPATFULL
TI Patterned thin film and process for preparing the same
IN Uekita, Masakazu, Kobe, Japan
Awaji, Hiroshi, Kobe, Japan
Murata, Makoto, Kobe, Japan
Mizunuma, Satoshi, Kobe, Japan
PA Kanegafuchi Kagaku Kogyo Kabushiki Kaisha, Osaka, Japan (non-U.S. corporation)
PI US 4943471 19900724
AI US 1988-248683 19880923 (7)
RLI Continuation-in-part of Ser. No. US 1987-51350, filed on 19 May 1987, now patented, Pat. No. US 4839219
PRAI JP 1986-116390 19860520
JP 1986-116391 19860520
JP 1987-241640 19870925
JP 1988-106048 19880428
DT Utility
LN.CNT 910
INCL INCLM: 428/220.000
INCLS: 428/411.100; 428/473.500; 528/183.000; 528/186.000; 528/188.000; 528/331.000; 528/342.000; 528/348.000; 528/350.000; 528/353.000
NCL NCLM: 428/220.000
NCLS: 136/263.000; 428/411.100; 428/473.500; 528/183.000; 528/186.000; 528/188.000; 528/331.000; 528/342.000; 528/348.000; 528/350.000; 528/353.000
IC [5]
ICM: B32B027-00
ICS: B32B027-34
EXF 428/199; 428/220; 428/473.5; 428/411.1; 528/186; 528/188; 528/350; 528/353; 528/331; 528/342; 528/348; 528/183
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 13 OF 13 USPATFULL
AN 89:47719 USPATFULL
TI Thin film and device having the same
IN Uekita, Masakazu, Kobe, Japan
Awaji, Hiroshi, Kobe, Japan
PA Kanegafuchi Kagaku Kogyo Kabushiki Kaisha, Osaka, Japan (non-U.S. corporation)
PI US 4839219 19890613
AI US 1987-51350 19870519 (7)
PRAI JP 1986-116390 19860520
JP 1986-116391 19860520
DT Utility
LN.CNT 1718

INCL INCLM: 428/220.000
INCLS: 428/411.100; 428/473.500; 528/183.000; 528/186.000; 528/188.000;
528/331.000; 528/342.000; 528/348.000; 528/350.000; 528/353.000
NCL NCLM: 428/220.000
NCLS: 136/255.000; 428/411.100; 428/473.500; 528/183.000; 528/186.000;
528/188.000; 528/331.000; 528/342.000; 528/348.000; 528/350.000;
528/353.000
IC [4]
ICM: B32B027-00
ICS: B32B027-34
EXF 428/473.5; 428/411.1; 428/220; 528/183; 528/186; 528/188; 528/350;
528/353; 528/331; 528/342; 528/348
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> s polymer structure#

278356 POLYMER
1253435 STRUCTURE#
L1 4727 POLYMER STRUCTURE#
(POLYMER(W) STRUCTURE#)

=> s l1 and monomolecular layer#

2655 MONOMOLECULAR
708881 LAYER#
1319 MONOMOLECULAR LAYER#
(MONOMOLECULAR(W) LAYER#)
L2 21 L1 AND MONOMOLECULAR LAYER#

=> s l2 and z axis

260791 Z
792308 AXIS
23922 Z AXIS
(Z(W) AXIS)
L3 0 L2 AND Z AXIS

=> s l2 and axial#

388074 AXIAL#
L4 0 L2 AND AXIAL#

=> s l2 and covalent?

40488 COVALENT?
L5 8 L2 AND COVALENT?

=> d 15 1-8

L5 ANSWER 1 OF 8 USPATFULL
AN 96:31696 USPATFULL
TI Infrared imaging materials
IN Robillard, Jean J., El Paso, TX, United States
PA Board of Regents, The University of Texas System, Austin, TX, United States (U.S. corporation)
PI US 5508145 19960416
AI US 1995-447265 19950522 (8)
RLI Continuation of Ser. No. US 1992-973026, filed on 6 Nov 1992, now patented, Pat. No. US 5434032
DT Utility
LN.CNT 688
INCL INCLM: 430/345.000
INCLS: 430/495.000; 430/944.000; 430/962.000; 252/586.000
NCL NCLM: 430/345.000
NCLS: 252/586.000; 430/495.100; 430/944.000; 430/962.000
IC [6]
ICM: G03C001-685

EXF 430/345; 430/346; 430/495; 430/944; 430/962; 252/586; 252/587; 250/330;
250/316.1

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 2 OF 8 USPATFULL

AN 95:64802 USPATFULL

TI Infrared imaging methods and systems

IN Robillard, Jean J., El Paso, TX, United States

PA Board of Regents, The University of Texas System, Austin, TX, United States (U.S. corporation)

PI US 5434032 19950718

AI US 1992-973026 19921106 (7)

DT Utility

LN.CNT 741

INCL INCLM: 430/345.000

INCLS: 430/347.000; 430/962.000; 250/330.000; 250/316.100; 252/586.000

NCL NCLM: 430/345.000

NCLS: 250/316.100; 250/330.000; 252/586.000; 430/347.000; 430/962.000

IC [6]

ICM: G03C001-685

EXF 430/345; 430/347; 430/962; 250/330; 250/316.1; 252/586

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 3 OF 8 USPATFULL

AN 95:29552 USPATFULL

TI Biocompatible, low protein adsorption affinity matrix

IN Braatz, James A., Beltsville, MD, United States

Heifetz, Aaron H., Columbia, MD, United States

PA W. R. Grace & Co.-Conn., New York, NY, United States (U.S. corporation)

PI US 5403750 19950404

AI US 1991-682502 19910408 (7)

RLI Continuation-in-part of Ser. No. US 1991-665498, filed on 6 Mar 1991, now patented, Pat. No. US 5169720

DT Utility

LN.CNT 1432

INCL INCLM: 436/531.000

INCLS: 528/048.000; 528/052.000; 528/053.000; 528/059.000; 528/904.000;
427/002.130; 427/207.100; 427/221.000; 427/435.000; 210/500.240;
428/423.100; 428/423.900; 428/424.200; 428/424.600; 428/425.100;
428/425.500; 428/425.600; 604/008.000; 604/019.000; 604/403.000;
435/174.000; 435/176.000; 435/181.000; 435/182.000; 525/403.000;
525/418.000; 525/420.000; 525/424.000; 525/454.000; 436/120.000;
436/129.000; 436/131.000

NCL NCLM: 436/531.000

NCLS: 210/500.240; 427/002.130; 427/207.100; 427/221.000; 427/435.000;
428/423.100; 428/423.900; 428/424.200; 428/424.600; 428/425.100;
428/425.500; 428/425.600; 435/174.000; 435/176.000; 435/181.000;
435/182.000; 436/120.000; 436/129.000; 436/131.000; 525/403.000;
525/418.000; 525/420.000; 525/424.000; 525/454.000; 528/048.000;
528/052.000; 528/053.000; 528/059.000; 528/904.000; 604/008.000;
604/019.000; 604/403.000

IC [6]

ICM: G01N033-545

EXF 528/48; 528/52; 528/53; 528/59; 528/904; 427/2; 427/207.1; 427/221;
427/435; 210/500.24; 428/423.1; 428/423.9; 428/424.2; 428/424.6;

428/425.1; 428/425.5; 428/425.6; 604/8; 604/19; 604/403; 435/174;
435/176; 435/181; 435/182; 525/403; 525/418; 525/420; 525/424; 525/454;
436/531; 436/120; 436/128; 436/131

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 4 OF 8 USPATFULL

AN 91:98251 USPATFULL

TI Ultraporous thin-film membranes

IN Wrasidlo, Wolfgang J., LaJolla, CA, United States
PA Memtec America Corporation, Timonium, MD, United States (U.S. corporation)
PI US 5069945 19911203
AI US 1989-439935 19891121 (7)
RLI Division of Ser. No. US 1986-920365, filed on 20 Oct 1986, now patented,
Pat. No. US 4814012 which is a division of Ser. No. US 1988-232930, filed on 9 Aug 1988, now patented, Pat. No. US 4902424
DT Utility
LN.CNT 1230
INCL INCLM: 427/245.000
INCLS: 210/490.000; 210/500.370; 210/500.410
NCL NCLM: 427/245.000
NCLS: 210/490.000; 210/500.370; 210/500.410
IC [5]
ICM: B01D067-00
EXF 210/490; 210/500.37; 210/500.41; 427/245; 427/246; 264/41; 264/49
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 5 OF 8 USPATFULL
AN 90:54633 USPATFULL
TI Chemically modified hydrophilic prepolymers and polymers
IN Braatz, James A., Beltsville, MD, United States
Heifetz, Aaron H., Columbia, MD, United States
Wolfe, Richard A., Ellisville, MO, United States
Luthra, Narender P., Columbia, MD, United States
PA W. R. Grace & Co.-Conn, New York, NY, United States (U.S. corporation)
PI US 4940737 19900710
AI US 1988-266445 19881102 (7)
DT Utility
LN.CNT 1550
INCL INCLM: 521/103.000
INCLS: 521/129.000; 521/159.000; 521/905.000; 524/839.000; 524/591.000;
524/498.000; 528/053.000; 528/057.000; 528/059.000; 528/904.000
NCL NCLM: 521/103.000
NCLS: 521/129.000; 521/159.000; 521/905.000; 524/498.000; 524/591.000;
524/839.000; 528/053.000; 528/057.000; 528/059.000; 528/904.000
IC [5]
ICM: C08G018-14
EXF 521/905; 521/159; 521/129; 521/103; 524/916; 524/839; 524/591; 524/498;
528/53; 528/904; 528/49; 528/57; 528/59; 527/202
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 6 OF 8 USPATFULL
AN 90:42602 USPATFULL
TI Cell growth enhancers and/or antibody production stimulators comprising chemically modified hydrophilic polyurea-urethane prepolymers and polymers
IN Heifetz, Aaron H., Columbia, MD, United States
Wolfe, Richard A., Ellisville, MO, United States
Braatz, James A., Beltsville, MD, United States
Luthra, Narender P., Columbia, MD, United States
PA W. R. Grace & Co.-Conn., New York, NY, United States (U.S. corporation)
PI US 4929706 19900529
AI US 1989-319458 19890303 (7)
RLI Continuation-in-part of Ser. No. US 1988-266445, filed on 2 Nov 1988
DT Utility
LN.CNT 2101
INCL INCLM: 528/049.000
INCLS: 528/060.000; 528/066.000
NCL NCLM: 528/049.000
NCLS: 528/060.000; 528/066.000

IC [5]
ICM: C08G018-10
EXF 528/49; 528/60; 528/66
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 7 OF 8 USPATFULL
AN 90:13161 USPATFULL
TI Ultrafiltration thin film membranes
IN Wrasidlo, Wolfgang J., LaJolla, CA, United States
PA Memetc North America Corp., Timonium, MD, United States (U.S. corporation)
PI US 4902424 19900220
AI US 1988-232930 19880809 (7)
RLI Division of Ser. No. US 1986-920365, filed on 26 Oct 1986, now patented,
Pat. No. US 4814082
DT Utility
LN.CNT 1185
INCL INCLM: 210/500.360
INCLS: 210/500.370; 210/500.380; 210/500.410
NCL NCLM: 210/500.360
NCLS: 210/500.370; 210/500.380; 210/500.410
IC [4]
ICM: B01D013-00
EXF 210/500.41; 210/500.21; 210/500.34; 210/638; 210/654; 210/500.37; 210/500.36; 210/500.38
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 8 OF 8 USPATFULL
AN 89:20921 USPATFULL
TI Ultrafiltration thin film membranes
IN Wrasidlo, Wolfgang J., San Diego, CA, United States
PA Memtec North America Corporation, Timonium, MD, United States (U.S. corporation)
PI US 4814082 19890321
AI US 1986-920365 19861020 (6)
DT Utility
LN.CNT 1358
INCL INCLM: 210/490.000
INCLS: 210/500.370; 210/500.410
NCL NCLM: 210/490.000
NCLS: 210/500.370; 210/500.410
IC [4]
ICM: B01D013-00
EXF 210/500.41; 210/500.37; 210/490
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> d 12 1-21

L2 ANSWER 1 OF 21 USPATFULL
AN 1998:131915 USPATFULL
TI Method for matrix-assisted laser desorption ionization
IN Koster, Claus, Lilienthal, Germany, Federal Republic of
Franzen, Jochen, Bremen, Germany, Federal Republic of
PA Bruker-Franzen Analytik, GmbH, Bremen, Germany, Federal Republic of (non-U.S. corporation)
PI US 5828063 19981027
AI US 1997-832469 19970402 (8)
PRAI DE 1996-19617011 19960427
DT Utility
LN.CNT 491

INCL INCLM: 250/288.000
NCL NCLM: 250/288.000
IC [6]
ICM: H01J049-10
EXF 250/288; 250/288A; 250/281; 250/282
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 2 OF 21 USPATFULL
AN 96:45832 USPATFULL
TI Multilayer second-order nonlinear optical films of head-to-head,
mainchain chromophoric polymers
IN Wynne, Kenneth J., Fairfax County, VA, United States
Lindsay, Geoffrey A., Ridgecrest, CA, United States
Hoover, James M., Ridgecrest, CA, United States
Stenger-Smith, John, Ridgecrest, CA, United States
Henry, deceased, Ronald A., late of Ridgecrest, CA, United States by
Ann H. Henry, legal representative
Chafin, Andrew P., Ridgecrest, CA, United States
PA The United States of America as represented by the Secretary of the
Navy, Washington, DC, United States (U.S. government)
PI US 5520968 19960528
AI US 1995-435913 19950505 (8)
DT Utility
LN.CNT 1173
INCL INCLM: 428/001.000
INCLS: 359/326.000; 359/328.000; 428/333.000; 427/434.300
NCL NCLM: 428/001.310
NCLS: 359/326.000; 359/328.000; 427/434.300; 428/333.000
IC [6]
ICM: G02F001-35
EXF 359/326; 359/328; 428/1; 428/333; 427/434.3
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 3 OF 21 USPATFULL
AN 96:31696 USPATFULL
TI Infrared imaging materials
IN Robillard, Jean J., El Paso, TX, United States
PA Board of Regents, The University of Texas System, Austin, TX, United
States (U.S. corporation)
PI US 5508145 19960416
AI US 1995-447265 19950522 (8)
RLI Continuation of Ser. No. US 1992-973026, filed on 6 Nov 1992, now
patented, Pat. No. US 5434032
DT Utility
LN.CNT 688
INCL INCLM: 430/345.000
INCLS: 430/495.000; 430/944.000; 430/962.000; 252/586.000
NCL NCLM: 430/345.000
NCLS: 252/586.000; 430/495.100; 430/944.000; 430/962.000
IC [6]
ICM: G03C001-685
EXF 430/345; 430/346; 430/495; 430/944; 430/962; 252/586; 252/587; 250/330;
250/316.1
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 4 OF 21 USPATFULL
AN 95:64802 USPATFULL
TI Infrared imaging methods and systems
IN Robillard, Jean J., El Paso, TX, United States
PA Board of Regents, The University of Texas System, Austin, TX, United
States (U.S. corporation)
PI US 5434032 19950718
AI US 1992-973026 19921106 (7)

DT Utility
LN.CNT 741
INCL INCLM: 430/345.000
INCLS: 430/347.000; 430/962.000; 250/330.000; 250/316.100; 252/586.000
NCL NCLM: 430/345.000
NCLS: 250/316.100; 250/330.000; 252/586.000; 430/347.000; 430/962.000
IC [6]
ICM: G03C001-685
EXF 430/345; 430/347; 430/962; 250/330; 250/316.1; 252/586
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 5 OF 21 USPATFULL
AN 95:45210 USPATFULL
TI Solid state ion sensor with polyimide membrane
IN Brown, Richard B., Ann Arbor, MI, United States
Cha, Geun-Sig, Ann Arbor, MI, United States
PA The Board of Regents of The University of Michigan, Ann Arbor, MI,
United States (U.S. corporation)
PI US 5417835 19950523
AI US 1993-137373 19931014 (8)
RLI Continuation of Ser. No. US 1991-746134, filed on 13 Aug 1991, now
abandoned And a continuation of Ser. No. US 1989-370897, filed on 23
Jun 1989, now abandoned

DT Utility
LN.CNT 656
INCL INCLM: 204/403.000
INCLS: 204/418.000; 257/253.000; 257/414.000; 435/817.000
NCL NCLM: 204/403.000
NCLS: 204/418.000; 257/253.000; 257/414.000; 435/817.000
IC [6]
ICM: G01N027-26
EXF 204/418; 204/416; 204/403; 257/253; 257/414; 435/288; 435/291; 435/817
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 6 OF 21 USPATFULL
AN 95:34267 USPATFULL
TI Fluoropolymers
IN Beckerbauer, Richard, Wilmington, DE, United States
PA E. I. Du Pont de Nemours and Company, Wilmington, DE, United States
(U.S. corporation)
PI US 5408021 19950418
AI US 1993-149593 19931110 (8)
RLI Division of Ser. No. US 1991-728400, filed on 11 Jul 1991, now
patented,
Pat. No. US 5294493, issued on 15 Mar 1994 which is a
continuation-in-part of Ser. No. US 1990-625586, filed on 7 Dec 1990,
now abandoned

DT Utility
LN.CNT 1101
INCL INCLM: 526/243.000
INCLS: 252/299.010
NCL NCLM: 526/243.000
NCLS: 252/299.010
IC [6]
ICM: C08F126-00
EXF 526/243
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 7 OF 21 USPATFULL
AN 95:29552 USPATFULL
TI Biocompatible, low protein adsorption affinity matrix
IN Braatz, James A., Beltsville, MD, United States
Heifetz, Aaron H., Columbia, MD, United States

PA W. R. Grace & Co.-Conn., New York, NY, United States (U.S. corporation)
 PI US 5403750 19950404
 AI US 1991-682502 19910408 (7)
 RLI Continuation-in-part of Ser. No. US 1991-665498, filed on 6 Mar 1991,
 now patented, Pat. No. US 5169720
 DT Utility
 LN.CNT 1432
 INCL INCLM: 436/531.000
 INCLS: 528/048.000; 528/052.000; 528/053.000; 528/059.000; 528/904.000;
 427/002.130; 427/207.100; 427/221.000; 427/435.000; 210/500.240;
 428/423.100; 428/423.900; 428/424.200; 428/424.600; 428/425.100;
 428/425.500; 428/425.600; 604/008.000; 604/019.000; 604/403.000;
 435/174.000; 435/176.000; 435/181.000; 435/182.000; 525/403.000;
 525/418.000; 525/420.000; 525/424.000; 525/454.000; 436/120.000;
 436/129.000; 436/131.000
 NCL NCLM: 436/531.000
 NCLS: 210/500.240; 427/002.130; 427/207.100; 427/221.000; 427/435.000;
 428/423.100; 428/423.900; 428/424.200; 428/424.600; 428/425.100;
 428/425.500; 428/425.600; 435/174.000; 435/176.000; 435/181.000;
 435/182.000; 436/120.000; 436/129.000; 436/131.000; 525/403.000;
 525/418.000; 525/420.000; 525/424.000; 525/454.000; 528/048.000;
 528/052.000; 528/053.000; 528/059.000; 528/904.000; 604/008.000;
 604/019.000; 604/403.000
 IC [6]
 ICM: G01N033-545
 EXF 528/48; 528/52; 528/53; 528/59; 528/904; 427/2; 427/207.1; 427/221;
 427/435; 210/500.24; 428/423.1; 428/423.9; 428/424.2; 428/424.6;
 428/425.1; 428/425.5; 428/425.6; 604/8; 604/19; 604/403; 435/174;
 435/176; 435/181; 435/182; 525/403; 525/418; 525/420; 525/424; 525/454;
 436/531; 436/120; 436/128; 436/131
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.
 L2 ANSWER 8 OF 21 USPATFULL
 AN 94:22128 USPATFULL
 TI Polymeric films for second order nonlinear optics
 IN Beckerbauer, Richard, Wilmington, DE, United States
 Hsiung, Hui, Wilmington, DE, United States
 Kaku, Mureo, Wilmington, DE, United States
 Rodriguez Parada, Jose M., Wilmington, DE, United States
 Tam, Wilson, Boothwyn, PA, United States
 PA E. I. Du Pont de Nemours and Company, Wilmington, DE, United States
 (U.S. corporation)
 PI US 5294493 19940315
 AI US 1991-728400 19910711 (7)
 RLI Continuation-in-part of Ser. No. US 1990-623586, filed on 7 Dec 1990,
 now abandoned
 DT Utility
 LN.CNT 1182
 INCL INCLM: 428/411.100
 INCLS: 428/421.000; 428/422.000; 428/515.000; 428/520.000; 428/522.000;
 428/913.000
 NCL NCLM: 428/411.100
 NCLS: 428/421.000; 428/422.000; 428/515.000; 428/520.000; 428/522.000;
 428/913.000
 IC [5]
 ICM: B32B009-04
 EXF 428/411.1; 428/421; 428/913; 428/515; 428/520; 428/522; 428/422
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.
 L2 ANSWER 9 OF 21 USPATFULL
 AN 94:18802 USPATFULL
 TI Electro-optic waveguide deflector using a nonlinear optic film or
 liquid-crystal overlay cell for use in an optical pickup head

IN Revelli, Jr., Joseph F., Rochester, NY, United States
 Penner, Thomas L., Fairport, NY, United States
 Armstrong, Nancy J., Ontario, NY, United States
 Robello, Douglas R., Webster, NY, United States
 Schildkraut, Jay S., Rochester, NY, United States
 PA Eastman Kodak Company, Rochester, NY, United States (U.S. corporation)
 PI US 5291567 19940301
 AI US 1992-916422 19920721 (7)
 DT Utility
 LN.CNT 1317
 INCL INCLM: 385/008.000
 INCLS: 385/014.000; 385/143.000
 NCL NCLM: 385/008.000
 NCLS: 385/014.000; 385/143.000
 IC [5]
 ICM: G02B006-10
 EXF 385/8; 385/14; 385/143
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 10 OF 21 USPATFULL
 AN 93:20643 USPATFULL
 TI Organic nonlinear optical material
 IN Yoshimura, Tetsuzo, Machida, Japan
 PA Fujitsu Limited, Kanagawa, Japan (non-U.S. corporation)
 PI US 5194548 19930316
 AI US 1990-470477 19900126 (7)
 PRAI JP 1989-16352 19890127
 JP 1989-66022 19890320
 JP 1989-66042 19890320
 JP 1989-66048 19890320
 DT Utility
 LN.CNT 1858
 INCL INCLM: 526/285.000
 INCLS: 430/020.000; 526/310.000; 526/311.000; 526/312.000; 526/258.000;
 359/241.000; 359/245.000; 359/280.000
 NCL NCLM: 526/285.000
 NCLS: 359/241.000; 359/245.000; 359/280.000; 430/020.000; 526/258.000;
 526/310.000; 526/311.000; 526/312.000
 IC [5]
 ICM: C08F038-02
 ICS: C08F238-02
 EXF 526/285; 526/310; 526/311; 526/312; 526/258; 430/20
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 11 OF 21 USPATFULL
 AN 91:98251 USPATFULL
 TI Ultraporous thin-film membranes
 IN Wrasidlo, Wolfgang J., LaJolla, CA, United States
 PA Memtec America Corporation, Timonium, MD, United States (U.S. corporation)
 PI US 5069945 19911203
 AI US 1989-439935 19891121 (7)
 RLI Division of Ser. No. US 1986-920365, filed on 20 Oct 1986, now patented,
 Pat. No. US 4814012 which is a division of Ser. No. US 1988-232930, filed on 9 Aug 1988, now patented, Pat. No. US 4902424
 DT Utility
 LN.CNT 1230
 INCL INCLM: 427/245.000
 INCLS: 210/490.000; 210/500.370; 210/500.410
 NCL NCLM: 427/245.000
 NCLS: 210/490.000; 210/500.370; 210/500.410
 IC [5]

ICM: B01D067-00
EXF 210/490; 210/500.37; 210/500.41; 427/245; 427/246; 264/41; 264/49
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 12 OF 21 USPATFULL
AN 90:54633 USPATFULL
TI Chemically modified hydrophilic prepolymers and polymers
IN Braatz, James A., Beltsville, MD, United States
Heifetz, Aaron H., Columbia, MD, United States
Wolfe, Richard A., Ellisville, MO, United States
Luthra, Narender P., Columbia, MD, United States
PA W. R. Grace & Co.-Conn, New York, NY, United States (U.S. corporation)
PI US 4940737 19900710
AI US 1988-266445 19881102 (7)
DT Utility
LN.CNT 1550
INCL INCLM: 521/103.000
INCLS: 521/129.000; 521/159.000; 521/905.000; 524/839.000; 524/591.000;
524/498.000; 528/053.000; 528/057.000; 528/059.000; 528/904.000
NCL NCLM: 521/103.000
NCLS: 521/129.000; 521/159.000; 521/905.000; 524/498.000; 524/591.000;
524/839.000; 528/053.000; 528/057.000; 528/059.000; 528/904.000
IC [5]
ICM: C08G018-14
EXF 521/905; 521/159; 521/129; 521/103; 524/916; 524/839; 524/591; 524/498;
528/53; 528/904; 528/49; 528/57; 528/59; 527/202
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 13 OF 21 USPATFULL
AN 90:42602 USPATFULL
TI Cell growth enhancers and/or antibody production stimulators comprising
chemically modified hydrophilic polyurea-urethane prepolymers and
polymers
IN Heifetz, Aaron H., Columbia, MD, United States
Wolfe, Richard A., Ellisville, MO, United States
Braatz, James A., Beltsville, MD, United States
Luthra, Narender P., Columbia, MD, United States
PA W. R. Grace & Co.-Conn., New York, NY, United States (U.S. corporation)
PI US 4929706 19900529
AI US 1989-319458 19890303 (7)
RLI Continuation-in-part of Ser. No. US 1988-266445, filed on 2 Nov 1988
DT Utility
LN.CNT 2101
INCL INCLM: 528/049.000
INCLS: 528/060.000; 528/066.000
NCL NCLM: 528/049.000
NCLS: 528/060.000; 528/066.000
IC [5]
ICM: C08G018-10
EXF 528/49; 528/60; 528/66
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 14 OF 21 USPATFULL
AN 90:13161 USPATFULL
TI Ultrafiltration thin film membranes
IN Wrasidlo, Wolfgang J., LaJolla, CA, United States
PA Memetc North America Corp., Timonium, MD, United States (U.S.
corporation)
PI US 4902424 19900220
AI US 1988-232930 19880809 (7)
RLI Division of Ser. No. US 1986-920365, filed on 26 Oct 1986, now
patented,
Pat. No. US 4814082

DT Utility
LN.CNT 1185
INCL INCLM: 210/500.360
INCLS: 210/500.370; 210/500.380; 210/500.410
NCL NCLM: 210/500.360
NCLS: 210/500.370; 210/500.380; 210/500.410
IC [4]
ICM: B01D013-00
EXF 210/500.41; 210/500.21; 210/500.34; 210/638; 210/654; 210/500.37;
210/500.36; 210/500.38
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 15 OF 21 USPATFULL
AN 89:20921 USPATFULL
TI Ultrafiltration thin film membranes
IN Wrasidlo, Wolfgang J., San Diego, CA, United States
PA Memtec North America Corporation, Timonium, MD, United States (U.S. corporation)
PI US 4814082 19890321
AI US 1986-920365 19861020 (6)
DT Utility
LN.CNT 1358
INCL INCLM: 210/490.000
INCLS: 210/500.370; 210/500.410
NCL NCLM: 210/490.000
NCLS: 210/500.370; 210/500.410
IC [4]
ICM: B01D013-00
EXF 210/500.41; 210/500.37; 210/490
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 16 OF 21 USPATFULL
AN 86:38278 USPATFULL
TI Material containing microaggregates of metals, inorganic compounds or organometallic compounds, more particularly usable in heterogeneous catalysis and its production process
IN Barraud, Andre, Bures-sur-Yvette, France
Leloup, Jean, Gif sur Yvette, France
Ruaudel, Annie, Verrieres le Buisson, France
PA Commissariat a l'Energie Atomique, Paris, France (non-U.S. government)
PI US 4598056 19860701
AI US 1984-680354 19841211 (6)
PRAI FR 1983-19841 19831212
DT Utility
LN.CNT 558
INCL INCLM: 502/004.000
INCLS: 502/101.000; 502/527.000
NCL NCLM: 502/004.000
NCLS: 502/101.000; 502/527.240
IC [4]
ICM: B01J035-02
EXF 502/4; 502/101; 502/527
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 17 OF 21 USPATFULL
AN 85:4727 USPATFULL
TI Primary system
IN Rohowetz, Stanley E., Neenah, WI, United States
PA American Can Company, Greenwich, CT, United States (U.S. corporation)
PI US 4495156 19850122
AI US 1983-455649 19830105 (6)
DT Utility
LN.CNT 252

INCL INCLM: 427/384.000
INCLS: 106/287.190; 252/032.000; 260/429.500; 427/417.000; 427/419.800
NCL NCLM: 556/014.000
NCLS: 106/287.190; 427/417.000; 427/419.800; 556/028.000; 556/031.000
IC [3]
ICM: B05D001-36
ICS: B05D007-00; B05D003-02
EXF 148/6.14R; 148/6.2; 427/388.2; 427/388.4; 427/399; 427/409; 427/407.1;
427/27; 427/384; 427/417; 427/419.8; 106/287.19; 260/429.5; 252/32
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 18 OF 21 USPATFULL
AN 84:28589 USPATFULL
TI Absorbent products, processes and compositions
IN Korpman, Ralf, Bridgewater, NJ, United States
PA Johnson & Johnson, New Brunswick, NJ, United States (U.S. corporation)
PI US 4449977 19840522
AI US 1981-329642 19811211 (6)
RLI Continuation-in-part of Ser. No. US 1979-88882, filed on 29 Oct 1979,
now abandoned
DT Utility
LN.CNT 777
INCL INCLM: 604/366.000
INCLS: 604/370.000
NCL NCLM: 604/366.000
NCLS: 604/370.000
IC [3]
ICM: A61F013-16
EXF 604/327; 604/329; 604/330; 604/331; 604/358; 604/328; 604/366;
604/346-354; 604/370; 521/65; 521/84; 521/905; 521/916; 260/17R;
260/17.4BB; 260/17.4ST; 260/17.4UC

L2 ANSWER 19 OF 21 USPATFULL
AN 82:10703 USPATFULL
TI Absorbent products
IN Korpman, Ralf, Bridgewater, NJ, United States
PA Permacel, New Brunswick, NJ, United States (U.S. corporation)
PI US 4318408 19820309
AI US 1979-88881 19791029 (6)
DT Utility
LN.CNT 784
INCL INCLM: 128/287.000
INCLS: 128/285.000; 128/290.000P; 128/290.000B
NCL NCLM: 604/368.000
NCLS: 604/370.000; 604/373.000; 604/904.000
IC [3]
ICM: A61F013-16
EXF 128/284; 128/287; 128/155; 128/156; 128/285; 128/290R; 128/290P;
128/290B; 128/296
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 20 OF 21 USPATFULL
AN 80:51295 USPATFULL
TI Primer system
IN Rohowetz, Stanley E., Barrington, IL, United States
PA American Can Company, Greenwich, CT, United States (U.S. corporation)
PI US 4228221 19801014
AI US 1979-26906 19790404 (6)
DT Utility
LN.CNT 348
INCL INCLM: 428/469.000
INCLS: 427/027.000; 427/054.100
NCL NCLM: 428/469.000

NCLS: 427/470.000; 427/485.000; 427/517.000
IC [2]
ICM: B05D003-06
EXF 427/54; 427/27; 204/158R; 106/287.19; 260/429.5; 428/469
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 21 OF 21 USPATFULL
AN 78:27961 USPATFULL
TI Encapsulation of critical chemicals
IN Leo, Thomas J., Yardley, PA, United States
Reynolds, Michael J., Morrisville, PA, United States
PA Wyrough and Loser, Inc., Trenton, NJ, United States (U.S. corporation)
PI US 4092285 19780530
AI US 1976-710115 19760730 (5)
DT Utility
LN.CNT 994
INCL INCLM: 260/028.500R
INCLS: 260/023.000XA; 260/023.700R; 260/023.700A; 260/028.500B;
260/031.800HR; 260/031.800R; 260/031.800DR; 260/033.600AQ;
260/033.600PQ; 260/033.600UA; 260/045.750N; 260/045.750V;
260/045.900QA; 260/045.900D; 260/045.700S; 260/045.700SW;
260/745.000; 260/757.000; 260/759.000; 427/212.000; 427/220.000;
427/221.000; 427/222.000; 260/031.800G
NCL NCLM: 523/334.000
NCLS: 427/212.000; 427/220.000; 427/221.000; 427/222.000; 523/200.000;
523/205.000; 524/274.000; 524/297.000; 524/418.000; 524/433.000;
524/489.000; 524/552.000; 524/574.000; 524/585.000; 524/925.000

IC [2]
ICM: C08L091-00
EXF 260/28.5R; 260/28.5B; 260/31.8HR; 260/31.8PQ; 260/31.8G; 260/31.8R;
260/31.8DR; 260/33.6AQ; 260/33.6PQ; 260/33.6UA; 260/23XA; 260/23.7R;
260/45.75N; 260/45.75V; 260/45.9QA; 260/45.9DI; 260/45.7S; 260/45.75W;
260/745; 260/757; 260/759; 260/23.7A; 427/212; 427/220; 427/221;
427/222
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> s 12 and epitax?

30650 EPITAX?
L6 1 L2 AND EPITAX?

=> d

L6 ANSWER 1 OF 1 USPATFULL
AN 93:20643 USPATFULL
TI Organic nonlinear optical material
IN Yoshimura, Tetsuzo, Machida, Japan
PA Fujitsu Limited, Kanagawa, Japan (non-U.S. corporation)
PI US 5194548 19930316
AI US 1990-470477 19900126 (7)
PRAI JP 1989-16352 19890127
JP 1989-66022 19890320
JP 1989-66042 19890320
JP 1989-66048 19890320
DT Utility
LN.CNT 1858
INCL INCLM: 526/285.000
INCLS: 430/020.000; 526/310.000; 526/311.000; 526/312.000; 526/258.000;
359/241.000; 359/245.000; 359/280.000
NCL NCLM: 526/285.000
NCLS: 359/241.000; 359/245.000; 359/280.000; 430/020.000; 526/258.000;

526/310.000; 526/311.000; 526/312.000
IC [5]
ICM: C08F038-02
ICS: C08F238-02
EXF 526/285; 526/310; 526/311; 526/312; 526/258; 430/20
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> s Burtman, Vladimir/in

L1 0 BURTMAN, VLADIMIR/IN

=> s molecular layer epitaxy

297144 MOLECULAR

625057 LAYER

9672 EPITAXY

L2 32 MOLECULAR LAYER EPITAXY
(MOLECULAR (W) LAYER (W) EPITAXY)

=> s l2 and z axis

250400 Z

769338 AXIS

22652 Z AXIS

(Z (W) AXIS)

L3 0 L2 AND Z AXIS

=> s l2 and z

250400 Z

L4 4 L2 AND Z

=> s l4 and (tetracarboxylic dianhydride or tetracarboxylic acid dianhydride)

5730 TETRACARBOXYLIC

6450 DIANHYDRIDE

1689 TETRACARBOXYLIC DIANHYDRIDE

(TETRACARBOXYLIC (W) DIANHYDRIDE)

5730 TETRACARBOXYLIC

506851 ACID

6450 DIANHYDRIDE

1375 TETRACARBOXYLIC ACID DIANHYDRIDE

(TETRACARBOXYLIC (W) ACID (W) DIANHYDRIDE)

L5 0 L4 AND (TETRACARBOXYLIC DIANHYDRIDE OR TETRACARBOXYLIC ACID DIANHYDRIDE)

=> s l2 and (tetracarboxylic dianhydride or tetracarboxylic acid dianhydride)

5730 TETRACARBOXYLIC

6450 DIANHYDRIDE

1689 TETRACARBOXYLIC DIANHYDRIDE

(TETRACARBOXYLIC (W) DIANHYDRIDE)

5730 TETRACARBOXYLIC

506851 ACID

6450 DIANHYDRIDE

1375 TETRACARBOXYLIC ACID DIANHYDRIDE

(TETRACARBOXYLIC (W) ACID (W) DIANHYDRIDE)

L6 0 L2 AND (TETRACARBOXYLIC DIANHYDRIDE OR TETRACARBOXYLIC ACID DIANHYDRIDE)

=> s l2 and bismaleimide#

2466 BISMALEIMIDE#
L7 0 L2 AND BISMALEIMIDE#

=> s 12 and diamino carbozole#

17618 DIAMINO
176 CARBOZOLE#
0 DIAMINO CARBOZOLE#
(DIAMINO(W) CARBOZOLE#)
L8 0 L2 AND DIAMINO CARBOZOLE#

=> d 14 1-4

L4 ANSWER 1 OF 4 USPATFULL
AN 2000:57621 USPATFULL
TI Molecular wire injection sensors
IN Keen, Randy E., San Diego, CA, United States
PA Keensense, Inc., San Diego, CA, United States (U.S. corporation)
PI US 6060327 20000509
AI US 1997-856822 19970514 (8)
DT Utility
LN.CNT 2968
INCL INCLM: 436/518.000
INCLS: 204/400.000; 204/403.000; 422/082.010; 422/082.020; 435/006.000;
435/287.100; 435/287.200; 436/149.000; 436/150.000; 436/151.000;
436/524.000; 436/525.000; 436/531.000; 436/806.000
NCL NCLM: 436/518.000
NCLS: 204/400.000; 204/403.000; 422/082.010; 422/082.020; 435/006.000;
435/287.100; 435/287.200; 436/149.000; 436/150.000; 436/151.000;
436/524.000; 436/525.000; 436/531.000; 436/806.000
IC [7]
ICM: G01N033-543
EXF 204/400; 204/403; 422/82.01; 422/82.02; 435/6; 435/287.1; 435/287.2;
436/518; 436/524; 436/525; 436/531; 436/149; 436/150; 436/151; 436/806
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L4 ANSWER 2 OF 4 USPATFULL
AN 1998:55176 USPATFULL
TI Light-emitting diode having narrow luminescence spectrum
IN Komoto, Satoshi, Tokyo, Japan
PA Kabushiki Kaisha Toshiba, Kawasaki, Japan (non-U.S. corporation)
PI US 5753940 19980519
AI US 1996-730060 19961015 (8)
PRAI JP 1995-267373 19951016
DT Utility
LN.CNT 748
INCL INCLM: 257/095.000
INCLS: 257/098.000; 257/103.000; 257/622.000
NCL NCLM: 257/095.000
NCLS: 257/098.000; 257/103.000; 257/622.000
IC [6]
ICM: H01L033-00
EXF 257/89; 257/95; 257/98; 257/103; 257/622; 257/623
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L4 ANSWER 3 OF 4 USPATFULL
AN 94:21922 USPATFULL
TI Process for forming a thin film of silicon
IN Nishizawa, Junichi, 6-16, Komegafukuro 1-chome, Sandai-shi, Miyagi-ken,
Japan
Abe, Hitoshi, 1-3, Otamayashita, Sendai, Japan

PA Suzuki, Soubei, 1-3, Otamayashita, Sendai-shi, Miyagi-ken, Japan
 Research Development Corporation of Japan, Tokyo, Japan (non-U.S. corporation)
 Nishizawa, Junichi, Miyagi, Japan (non-U.S. corporation)
 Oki Electric Industry Co., Ltd., Tokyo, Japan (non-U.S. corporation)
 Suzuki, Soubei, Miyagi, Japan (non-U.S. corporation)
 PI US 5294286 19940315
 AI US 1993-3308 19930112 (8)
 RLI Continuation-in-part of Ser. No. US 1990-551631, filed on 10 Jul 1990, now abandoned which is a continuation of Ser. No. US 1988-266228, filed on 28 Oct 1988, now abandoned which is a continuation of Ser. No. US 1985-759096, filed on 25 Jul 1985, now abandoned
 PRAI JP 1984-153978 19840726
 DT Utility
 LN.CNT 1043
 INCL INCLM: 156/610.000
 INCLS: 156/611.000; 156/613.000; 156/614.000; 156/DIG.064; 156/DIG.080; 437/108.000; 437/241.000; 427/255.100
 NCL NCLM: 117/093.000
 NCLS: 117/089.000; 117/102.000; 117/935.000; 438/925.000
 IC [5]
 ICM: C30B025-14
 EXF 156/610; 156/611; 156/613; 156/614; 156/DIG.73; 156/DIG.80; 156/DIG.64; 422/245; 423/53.1; 423/54.1; 423/86; 423/87; 423/248.1; 423/255.1; 118/725; 118/726; 219/411; 219/419; 437/108; 437/241
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L4 ANSWER 4 OF 4 USPATFULL
 AN 92:7155 USPATFULL
 TI Process for preparing a thin film of superconducting compound oxide
 IN Harada, Keizo, Hyogo, Japan
 Fujimori, Naoji, Hyogo, Japan
 Yazu, Shuji, Hyogo, Japan
 Jodai, Tetsuji, Hyogo, Japan
 PA Sumitomo Electric Industries, Ltd., Osaka, Japan (non-U.S. corporation)
 PI US 5084265 19920128
 AI US 1990-525217 19900516 (7)
 RLI Continuation of Ser. No. US 1988-235459, filed on 24 Aug 1988, now abandoned
 PRAI JP 1987-209841 19870824
 DT Utility
 LN.CNT 565
 INCL INCLM: 423/592.000
 INCLS: 075/010.110; 075/010.290; 075/010.640
 NCL NCLM: 505/473.000
 NCLS: 075/010.110; 075/010.290; 075/010.640; 423/263.000; 423/593.000; 505/480.000
 IC [5]
 ICM: C22B004-00
 EXF 075/10.13; 075/10.11; 075/10.29; 075/10.64; 423/592
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> d 12 1-32

L2 ANSWER 1 OF 32 USPATFULL
 AN 2000:154526 USPATFULL
 TI Semiconductor memory operating electrically and optically, retaining information without power supply
 IN Sakata, Haruhisa, Tokyo, Japan
 Nagao, Yasuyuki, Hasuda, Japan
 Matsushima, Yuichi, Tokorozawa, Japan

PA KDD Corporation, Tokyo, Japan (non-U.S. corporation)
 PI US 6147901 20001114
 AI US 1999-227618 19990108 (9)
 PRAI JP 1998-3471 19980109
 JP 1999-481 19990105
 DT Utility
 LN.CNT 1388
 INCL INCLM: 365/175.000
 INCLS: 365/106.000
 NCL NCLM: 365/175.000
 NCLS: 365/106.000
 IC [7]
 ICM: G11C011-36
 EXF 365/106; 365/112; 365/107; 365/171; 365/173; 365/175; 257/25; 257/85;
 257/113

L2 ANSWER 2 OF 32 USPATFULL
 AN 2000:146720 USPATFULL
 TI Semiconductor device and manufacturing method thereof
 IN Sugiura, Soichi, Mie-ken, Japan
 Watanobe, Hisashi, Mie-ken, Japan
 PA Kabushiki Kaisha Toshiba, Kanagawa-Ken, Japan (non-U.S. corporation)
 PI US 6140675 20001031
 AI US 1999-366357 19990803 (9)
 PRAI JP 1998-223311 19980806
 DT Utility
 LN.CNT 1136
 INCL INCLM: 257/301.000
 INCLS: 257/304.000
 NCL NCLM: 257/301.000
 NCLS: 257/304.000
 IC [7]
 ICM: H01L027-108
 ICS: H01L029-76
 EXF 257/301; 257/304

L2 ANSWER 3 OF 32 USPATFULL
 AN 2000:57621 USPATFULL
 TI Molecular wire injection sensors
 IN Keen, Randy E., San Diego, CA, United States
 PA Keensense, Inc., San Diego, CA, United States (U.S. corporation)
 PI US 6060327 20000509
 AI US 1997-856822 19970514 (8)
 DT Utility
 LN.CNT 2968
 INCL INCLM: 436/518.000
 INCLS: 204/400.000; 204/403.000; 422/082.010; 422/082.020; 435/006.000;
 435/287.100; 435/287.200; 436/149.000; 436/150.000; 436/151.000;
 436/524.000; 436/525.000; 436/531.000; 436/806.000
 NCL NCLM: 436/518.000
 NCLS: 204/400.000; 204/403.000; 422/082.010; 422/082.020; 435/006.000;
 435/287.100; 435/287.200; 436/149.000; 436/150.000; 436/151.000;
 436/524.000; 436/525.000; 436/531.000; 436/806.000
 IC [7]
 ICM: G01N033-543
 EXF 204/400; 204/403; 422/82.01; 422/82.02; 435/6; 435/287.1; 435/287.2;
 436/518; 436/524; 436/525; 436/531; 436/149; 436/150; 436/151; 436/806
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 4 OF 32 USPATFULL
 AN 1999:146999 USPATFULL
 TI Thin film capacitor with electrodes having a perovskite structure and a
 metallic conductivity

IN Fukushima, Noburu, Tokyo, Japan
 Kawakubo, Takashi, Kanagawa-ken, Japan
 Shimizu, Tatsuo, Kanagawa-ken, Japan
 PA Kabushiki Kaisha Toshiba, Kawasaki, Japan (non-U.S. corporation)
 PI US 5986301 19991116
 AI US 1997-858768 19970519 (8)
 RLI Continuation of Ser. No. US 1996-590566, filed on 26 Jan 1996, now
 abandoned
 PRAI JP 1995-11655 19950127
 JP 1995-235789 19950913
 DT Utility
 LN.CNT 2223
 INCL INCLM: 257/306.000
 INCLS: 257/295.000; 257/310.000
 NCL NCLM: 257/306.000
 NCLS: 257/295.000; 257/310.000
 IC [6]
 ICM: H01L027-108
 ICS: H01L029-76; H01L029-94; H01L031-119
 EXF 257/295; 257/296; 257/306; 257/310; 257/347
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 5 OF 32 USPATFULL
 AN 1999:81766 USPATFULL
 TI Method of producing a bipolar transistor
 IN Aoki, Kenji, Tokyo, Japan
 Akamine, Tadao, Tokyo, Japan
 Kojima, Yoshikazu, Tokyo, Japan
 PA Seiko Instruments Inc., Tokyo, Japan (non-U.S. corporation)
 PI US 5925574 19990720
 AI US 1992-865646 19920410 (7)
 RLI Continuation of Ser. No. US 1990-620624, filed on 3 Dec 1990, now
 abandoned
 PRAI JP 1989-313724 19891201
 JP 1989-313725 19891201
 DT Utility
 LN.CNT 519
 INCL INCLM: 437/031.000
 INCLS: 437/141.000; 437/160.000; 437/168.000; 148/DIG.017; 148/DIG.034;
 148/DIG.144
 NCL NCLM: 438/309.000
 NCLS: 148/DIG.017; 148/DIG.034; 148/DIG.144; 438/365.000; 438/558.000
 IC [6]
 ICM: H01L021-265
 EXF 437/31; 437/32; 437/141; 437/160; 437/168; 148/DIG.17; 148/DIG.158;
 148/DIG.144; 148/DIG.34
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 6 OF 32 USPATFULL
 AN 1999:79988 USPATFULL
 TI MOS field effect transistor and its manufacturing method
 IN Aoki, Kenji, Tokyo, Japan
 Takada, Ryoji, Tokyo, Japan
 PA Seiko Instruments Inc., Japan (non-U.S. corporation)
 PI US 5923985 19990713
 AI US 1997-782975 19970114 (8)
 RLI Division of Ser. No. US 1995-538980, filed on 5 Oct 1995 which is a
 continuation of Ser. No. US 1995-441656, filed on 15 May 1995, now
 abandoned which is a continuation of Ser. No. US 1994-216764, filed on
 22 Mar 1994, now abandoned which is a continuation of Ser. No. US
 1993-132485, filed on 6 Oct 1993, now abandoned which is a continuation
 of Ser. No. US 1993-58048, filed on 5 May 1993, now abandoned which is

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Jan 1988, now abandoned
PRAI JP 1987-321 19870105
JP 1987-7553 19870116
JP 1987-11861 19870121
JP 1987-36618 19870219
JP 1987-97960 19870421
JP 1987-119543 19870515
DT Utility
LN.CNT 313
INCL INCLM: 438/301.000
INCLS: 438/478.000
NCL NCLM: 438/301.000
NCLS: 438/478.000
IC [6]
ICM: H01L021-336
ICS: H01L021-20
EXF 438/142; 438/301; 438/305; 438/478
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 7 OF 32 USPATFULL
AN 1998:69423 USPATFULL
TI Electron-beam lithography system and method for drawing nanometer-order
pattern
IN Takeno, Shiro, Kanagawa-ken, Japan
Kanbayashi, Shigeru, Kanagawa-ken, Japan
Koike, Mitsuo, Kanagawa-ken, Japan
Doi, Seizo, Tokyo, Japan
Higashikawa, Iwao, Tokyo, Japan
PA Kabushiki Kaisha Toshiba, Kawasaki, Japan (non-U.S. corporation)
PI US 5767521 19980616
AI US 1995-528409 19950914 (8)
PRAI JP 1994-222254 19940916
JP 1995-232157 19950911
DT Utility
LN.CNT 784
INCL INCLM: 250/492.200
INCLS: 250/398.000
NCL NCLM: 250/492.200
NCLS: 250/398.000
IC [6]
ICM: H01J037-04
EXF 250/492.2; 250/492.22; 250/492.23; 250/398; 250/396R; 250/311; 250/306;
250/307

L2 ANSWER 8 OF 32 USPATFULL
AN 1998:55176 USPATFULL
TI Light-emitting diode having narrow luminescence spectrum
IN Komoto, Satoshi, Tokyo, Japan
PA Kabushiki Kaisha Toshiba, Kawasaki, Japan (non-U.S. corporation)
PI US 5753940 19980519
AI US 1996-730060 19961015 (8)
PRAI JP 1995-267373 19951016
DT Utility
LN.CNT 748
INCL INCLM: 257/095.000
INCLS: 257/098.000; 257/103.000; 257/622.000
NCL NCLM: 257/095.000
NCLS: 257/098.000; 257/103.000; 257/622.000
IC [6]
ICM: H01L033-00

EXF 257/89; 257/95; 257/98; 257/103; 257/622; 257/623
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 9 OF 32 USPATFULL
AN 97:118349 USPATFULL
TI Insulated-gate transistor having narrow-bandgap-source
IN Yoshimi, Makoto, Tokyo, Japan
Inaba, Satoshi, Tokyo, Japan
Murakoshi, Atsushi, Tokyo, Japan
Terauchi, Mamoru, Tokyo, Japan
Shigyo, Naoyuki, Tokyo, Japan
Matsushita, Yoshiaki, Tokyo, Japan
Aoki, Masami, Tokyo, Japan
Hamamoto, Takeshi, Tokyo, Japan
Ishibashi, Yutaka, Tokyo, Japan
Ozaki, Tohru, Tokyo, Japan
Kawaguchiya, Hitomi, Tokyo, Japan
Matsuzawa, Kazuya, Tokyo, Japan
Arisumi, Osamu, Tokyo, Japan
Nishiyama, Akira, Tokyo, Japan
PA Kabushiki Kaisha Toshiba, Kawasaki, Japan (non-U.S. corporation)
PI US 5698869 19971216
AI US 1995-527515 19950913 (8)
PRAI JP 1994-218513 19940913
JP 1994-218593 19940913
JP 1994-219073 19940913
JP 1994-305214 19941208
JP 1994-305241 19941208
JP 1995-230329 19950907
DT Utility
LN.CNT 4279
INCL INCLM: 257/192.000
INCLS: 257/066.000; 257/347.000; 257/616.000
NCL NCLM: 257/192.000
NCLS: 257/066.000; 257/347.000; 257/616.000
IC [6]
ICM: H01L031-072
EXF 257/63; 257/65; 257/347; 257/616; 257/631; 257/55; 257/607; 257/192;
257/66
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 10 OF 32 USPATFULL
AN 97:111983 USPATFULL
TI Growth of doped semiconductor monolayers
IN Nishizawa, Junichi, Miyai-ken, Japan
Abe, Hitoshi, Miyai-ken, Japan
Suzuki, Soubei, 1-3, Otamayahshita, Sendai-shi, Miyagi-ken, Japan
PA Research Development Corporation of Japan, Tokyo, Japan (non-U.S. corporation)
Nishizawa, Jun-Ichi, Sendai, Japan (non-U.S. individual)
Oki Electric Company, Tokyo, Japan (non-U.S. corporation)
Suzuki, Soubei, Sendai, Japan (non-U.S. individual)
PI US 5693139 19971202
AI US 1993-77119 19930615 (8)
RLI Continuation-in-part of Ser. No. US 1991-671995, filed on 18 Mar 1991, now abandoned And Ser. No. US 1990-482283, filed on 20 Feb 1990, now abandoned which is a continuation of Ser. No. US 1988-234002, filed on 12 Aug 1988, now abandoned which is a continuation of Ser. No. US 1985-759087, filed on 25 Jul 1985, now abandoned, said Ser. No. US -671995 which is a continuation of Ser. No. US 1989-372156, filed on 27 Jun 1989, now abandoned which is a continuation of Ser. No. US 1987-122997, filed on 19 Nov 1987, now abandoned
PRAI JP 1984-153977 19840726

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|--|-----------------|----------|
| | JP 1984-153980 | 19840726 |
| | GB 1985-18834 | 19850725 |
| | DE 1985-3526824 | 19850726 |
| | FR 1985-11517 | 19850726 |
| | JP 1986-275425 | 19861120 |
| | DE 1987-3739450 | 19871120 |
| | FR 1987-16124 | 19871120 |
| | GB 1987-27277 | 19871120 |

DT Utility

LN.CNT 1239

INCL INCLM: 117/089.000
INCLS: 117/093.000; 117/102.000; 117/105.000; 117/953.000; 117/954.000;
117/956.000; 437/102.000; 437/103.000

NCL NCLM: 117/089.000
NCLS: 117/093.000; 117/102.000; 117/105.000; 117/953.000; 117/954.000;
117/956.000

IC [6]
ICM: C30B025-14

EXF 437/102; 437/103; 427/243; 427/255.1; 117/953; 117/954; 117/956;
117/89;
117/93; 117/102; 117/105

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 11 OF 32 USPATFULL

AN 96:82299 USPATFULL

TI Method and apparatus using organic vapor phase deposition for the
growth
of organic thin films with large optical non-linearities

IN Forrest, Stephen R., Princeton, NJ, United States
Ban, Vladimir S., Princeton, NJ, United States
Burrows, Paul E., Princeton, NJ, United States
Schwartz, Jeffrey, Princeton, NJ, United States

PA The Trustees of Princeton University, Princeton, NJ, United States
(U.S.
corporation)

PI US 5554220 19960910

AI US 1995-444252 19950519 (8)

DT Utility

LN.CNT 805

INCL INCLM: 117/088.000
INCLS: 117/091.000; 117/099.000; 117/102.000; 117/104.000; 117/925.000;
117/926.000; 117/927.000

NCL NCLM: 117/088.000
NCLS: 117/091.000; 117/099.000; 117/102.000; 117/104.000; 117/925.000;
117/926.000; 117/927.000

IC [6]
ICM: C30B029-54

EXF 117/88; 117/91; 117/99; 117/102; 117/104; 117/925; 117/926; 117/927

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 12 OF 32 USPATFULL

AN 96:58484 USPATFULL

TI Semiconductor device comprising a highspeed static induction transistor

IN Nishizawa, Jun-ichi, 6-16, Komegafukuro 1-chome, Aoka-ku, Sendai-shi,
Miyagi-ken, 980, Japan
Kurabayashi, Toru, Sendai, Japan

PA Research Development Corp. of Japan, Tokyo, Japan (non-U.S.
corporation)
Nishzawa, Jun-ichi, Sendai, Japan (non-U.S. individual)
Zaidan Hojin Handotai Kenkyu Shinokai, Sendai, Japan (non-U.S.
corporation)

PI US 5532511 19960702

AI US 1995-409684 19950323 (8)

RLI Continuation of Ser. No. US 1993-162300, filed on 7 Dec 1993, now abandoned which is a division of Ser. No. US 1992-965722, filed on 23 Oct 1992, now patented, Pat. No. US 5296403
DT Utility
LN.CNT 676
INCL INCLM: 257/627.000
INCLS: 257/263.000; 257/264.000; 257/268.000; 257/628.000
NCL NCLM: 257/627.000
NCLS: 257/263.000; 257/264.000; 257/268.000; 257/628.000
IC [6]
ICM: H01L029-04
ICS: H01L029-80; H01L031-112; H01L031-036
EXF 257/138; 257/256; 257/263; 257/264; 257/268; 257/272; 257/265; 257/192; 257/183; 257/521; 257/627; 257/628
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 13 OF 32 USPATFULL
AN 96:53248 USPATFULL
TI Impurity doping method with adsorbed diffusion source
IN Nishizawa, Junichi, Miyagi, Japan
Aoki, Kenji, Tokyo, Japan
PA Seiko Instruments Inc., Tokyo, Japan (non-U.S. corporation)
PI US 5527733 19960618
AI US 1994-198379 19940218 (8)
RLI Continuation of Ser. No. US 1992-928525, filed on 11 Aug 1992, now abandoned which is a continuation of Ser. No. US 1990-558427, filed on 27 Jul 1990, now abandoned
DT Utility
LN.CNT 625
INCL INCLM: 437/160.000
INCLS: 437/939.000; 437/950.000
NCL NCLM: 438/558.000
IC [6]
ICM: H01L021-225
EXF 437/165; 437/166; 437/160; 437/937; 437/939; 437/942; 437/946; 437/950; 148/DIG.17; 148/DIG.34; 148/DIG.38; 148/DIG.144
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 14 OF 32 USPATFULL
AN 96:6013 USPATFULL
TI Semiconductor device and method of manufacturing same
IN Nishizawa, Jun-ichi, Sendai, Japan
PA Zaidan Hojin Handotai Kenkyu Shinkokai, Miyagi, Japan (non-U.S. corporation)
PI US 5485017 19960116
AI US 1994-241447 19940511 (8)
PRAI JP 1993-147128 19930512
DT Utility
LN.CNT 1327
INCL INCLM: 257/024.000
INCLS: 257/030.000; 257/038.000; 257/046.000; 257/104.000; 257/136.000; 257/498.000; 257/458.000; 257/523.000; 437/040.000; 437/081.000; 437/105.000; 437/107.000; 437/126.000; 437/228.000
NCL NCLM: 257/024.000
NCLS: 257/030.000; 257/038.000; 257/046.000; 257/104.000; 257/136.000; 257/458.000; 257/498.000; 257/523.000; 438/191.000; 438/192.000; 438/268.000
IC [6]
ICM: H01L029-06
ICS: H01L021-265
EXF 257/24; 257/30; 257/38; 257/46; 257/104; 257/136; 257/458; 257/523; 257/498; 437/40; 437/81; 437/105; 437/107; 437/126; 437/228
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 15 OF 32 USPATFULL
 AN 95:108393 USPATFULL
 TI Vertical insulated gate transistor and method of manufacture
 IN Kakumoto, Munenari, Kawasaki, Japan
 PA Kabushiki Kaisha Toshiba, Kawasaki, Japan (non-U.S. corporation)
 PI US 5473176 19951205
 AI US 1994-296913 19940831 (8)
 PRAI JP 1993-217604 19930901
 JP 1994-200470 19940825
 DT Utility
 LN.CNT 766
 INCL INCLM: 257/192.000
 INCLS: 257/263.000; 257/284.000; 257/330.000; 257/333.000; 257/341.000;
 257/622.000; 437/040.000; 437/107.000; 437/133.000; 437/703.000;
 437/228.000; 437/913.000
 NCL NCLM: 257/192.000
 NCLS: 257/263.000; 257/284.000; 257/330.000; 257/333.000; 257/341.000;
 257/622.000; 438/270.000; 438/271.000
 IC [6]
 ICM: H01L029-161
 ICS: H01L021-265
 EXF 257/284; 257/330; 257/333; 257/192; 257/263; 257/341; 257/622; 437/40;
 437/203; 437/107; 437/126; 437/133; 437/228; 437/913

L2 ANSWER 16 OF 32 USPATFULL
 AN 94:70981 USPATFULL
 TI Doping method of barrier region in semiconductor device
 IN Aoki, Kenji, Tokyo, Japan
 Akamine, Tadao, Tokyo, Japan
 Saito, Naoto, Tokyo, Japan
 PA Seiko Instruments Inc., Tokyo, Japan (non-U.S. corporation)
 PI US 5338697 19940816
 AI US 1990-620615 19901203 (7)
 PRAI JP 1989-313719 19891201
 JP 1989-313720 19891201
 JP 1989-313726 19891201
 JP 1989-318553 19891206
 JP 1989-318554 19891206
 DT Utility
 LN.CNT 1090
 INCL INCLM: 437/040.000
 INCLS: 437/041.000; 437/064.000; 437/069.000; 437/160.000; 437/161.000;
 437/950.000; 437/968.000; 148/DIG.037
 NCL NCLM: 438/291.000
 NCLS: 148/DIG.037; 438/298.000; 438/300.000
 IC [5]
 ICM: H01L021-76
 ICS: H01L021-336
 EXF 437/41; 437/44; 437/64; 437/69; 437/160; 437/161; 437/913; 437/950;
 437/968; 437/40; 148/DIG.34; 148/DIG.37; 148/DIG.53; 257/345; 257/398;
 257/399; 257/400; 257/648; 257/652
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 17 OF 32 USPATFULL
 AN 94:70676 USPATFULL
 TI Method of epitaxially growing compound crystal and doping method
 therein
 IN Nishizawa, Jun-ichi, Miyagi, Japan
 Kurabayashi, Toru, Miyagi, Japan
 PA Research Development Corporation of Japan, Tokyo, Japan (non-U.S.
 corporation)
 PI US 5338389 19940816

AI US 1993-49661 19930421 (8)
 RLI Continuation of Ser. No. US 1992-860253, filed on 31 Mar 1992, now abandoned which is a continuation of Ser. No. US 1991-642965, filed on 18 Jan 1991, now abandoned
 PRAI JP 1990-8399 19900119
 DT Utility
 LN.CNT 719
 INCL INCLM: 117/089.000
 INCLS: 117/953.000; 117/954.000; 117/955.000
 NCL NCLM: 117/089.000
 NCLS: 117/953.000; 117/954.000; 117/955.000
 IC [5]
 ICM: C30B025-02
 EXF 156/601; 156/610; 156/611; 156/612; 156/613; 156/614; 156/DIG.70; 156/DIG.73; 156/DIG.89
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 18 OF 32 USPATFULL
 AN 94:24239 USPATFULL
 TI Method of manufacturing a static induction field-effect transistor
 IN Nishizawa, Jun-ichi, Sendai, Japan
 Kurabayashi, Toru, Sendai, Japan
 PA Research Development Corp. of Japan, Tokyo, Japan (non-U.S. corporation)
 Jun-ichi Nishizawa, Miyagi, Japan (non-U.S. corporation)
 Zaidan Hojin Handotai Kenkyu Shinkokai, Miyagi, Japan (non-U.S. corporation)
 PI US 5296403 19940322
 AI US 1992-965722 19921023 (7)
 DT Utility
 LN.CNT 622
 INCL INCLM: 437/133.000
 INCLS: 437/909.000; 437/911.000; 437/913.000
 NCL NCLM: 438/198.000
 NCLS: 438/270.000
 IC [5]
 ICM: H01L021-20
 EXF 437/133; 437/107; 437/126; 437/90; 437/909; 437/911; 437/913
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 19 OF 32 USPATFULL
 AN 94:21922 USPATFULL
 TI Process for forming a thin film of silicon
 IN Nishizawa, Junichi, 6-16, Komegafukuro 1-chome, Sandai-shi, Miyagi-ken, Japan
 Abe, Hitoshi, 1-3, Otamayashita, Sendai, Japan
 Suzuki, Soubei, 1-3, Otamayashita, Sendai-shi, Miyagi-ken, Japan
 PA Research Development Corporation of Japan, Tokyo, Japan (non-U.S. corporation)
 Nishizawa, Junichi, Miyagi, Japan (non-U.S. corporation)
 Oki Electric Industry Co., Ltd., Tokyo, Japan (non-U.S. corporation)
 Suzuki, Soubei, Miyagi, Japan (non-U.S. corporation)
 PI US 5294286 19940315
 AI US 1993-3308 19930112 (8)
 RLI Continuation-in-part of Ser. No. US 1990-551631, filed on 10 Jul 1990, now abandoned which is a continuation of Ser. No. US 1988-266228, filed on 28 Oct 1988, now abandoned which is a continuation of Ser. No. US 1985-759096, filed on 25 Jul 1985, now abandoned
 PRAI JP 1984-153978 19840726
 DT Utility
 LN.CNT 1043
 INCL INCLM: 156/610.000
 INCLS: 156/611.000; 156/613.000; 156/614.000; 156/DIG.064; 156/DIG.080;

437/108.000; 437/241.000; 427/255.100
 NCL NCLM: 117/093.000
 NCLS: 117/089.000; 117/102.000; 117/935.000; 438/925.000
 IC [5]
 ICM: C30B025-14
 EXF 156/610; 156/611; 156/613; 156/614; 156/DIG.73; 156/DIG.80; 156/DIG.64;
 422/245; 423/53.1; 423/54.1; 423/86; 423/87; 423/248.1; 423/255.1;
 118/725; 118/726; 219/411; 219/419; 437/108; 437/241
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 20 OF 32 USPATFULL
 AN 93:86995 USPATFULL
 TI Method of epitaxially growing semiconductor crystal using light as a
 detector
 IN Nishizawa, Jun-ichi, 6-16, Komegafukuro 1-chome, Aoba-ku, Sendai-shi,
 Miyagi-ken, Japan
 Kurabayashi, Toru, Sendai, Japan
 PA Research Development Corporation of Japan, Tokyo, Japan (non-U.S.
 corporation)
 Nishizawa, Jun-ichi, Sendai, Japan (non-U.S. individual)
 Hojin, Zaidan, all of, Japan (non-U.S. individual)
 Shinkoka, Handotai Kenkyu, all of, Japan (non-U.S. individual)
 PI US 5254207 19931019
 AI US 1992-983331 19921130 (7)
 PRAI JP 1991-342448 19911130
 DT Utility
 LN.CNT 522
 INCL INCLM: 156/601.000
 INCLS: 156/612.000; 356/382.000; 356/318.000
 NCL NCLM: 117/086.000
 NCLS: 117/954.000; 356/318.000; 356/382.000
 IC [5]
 ICM: C30B023-02
 EXF 156/612; 156/601; 356/317; 356/318; 356/319; 356/330; 356/346; 356/382
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 21 OF 32 USPATFULL
 AN 93:78385 USPATFULL
 TI Method for growing single crystal thin films of element semiconductor
 IN Nishizawa, Junichi, 6-16, Komegafukuro 1-chome, Sendai-shi, Miyagi,
 Japan
 Aoki, Kenji, Matsudo, Japan
 PA Research Development Corporation of Japan, Tokyo, Japan (non-U.S.
 corporation)
 Nishizawa, Junichi, Tokyo, Japan (non-U.S. individual)
 Seiko Instruments*, Sendai, Japan (non-U.S. corporation)
 PI US 5246536 19930921
 AI US 1989-321623 19890310 (7)
 RLI Division of Ser. No. US 1987-93505, filed on 4 Sep 1987, now patented,
 Pat. No. US 4831831
 PRAI JP 1986-209575 19860908
 DT Utility
 LN.CNT 378
 INCL INCLM: 156/610.000
 INCLS: 156/611.000; 156/613.000; 156/614.000; 156/DIG.064; 437/241.000
 NCL NCLM: 117/102.000
 NCLS: 117/935.000
 IC [5]
 ICM: C30B025-14
 EXF 156/616; 156/611; 156/613; 156/614; 156/DIG.64; 427/255.1; 437/241
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 22 OF 32 USPATFULL

AN 93:20643 USPATFULL
 TI Organic nonlinear optical material
 IN Yoshimura, Tetsuzo, Machida, Japan
 PA Fujitsu Limited, Kanagawa, Japan (non-U.S. corporation)
 PI US 5194548 19930316
 AI US 1990-470477 19900126 (7)
 PRAI JP 1989-16352 19890127
 JP 1989-66022 19890320
 JP 1989-66042 19890320
 JP 1989-66048 19890320
 DT Utility
 LN.CNT 1858
 INCL INCLM: 526/285.000
 INCLS: 430/020.000; 526/310.000; 526/311.000; 526/312.000; 526/258.000;
 359/241.000; 359/245.000; 359/280.000
 NCL NCLM: 526/285.000
 NCLS: 359/241.000; 359/245.000; 359/280.000; 430/020.000; 526/258.000;
 526/310.000; 526/311.000; 526/312.000
 IC [5]
 ICM: C08F038-02
 ICS: C08F238-02
 EXF 526/285; 526/310; 526/311; 526/312; 526/258; 430/20
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 23 OF 32 USPATFULL
 AN 92:51014 USPATFULL
 TI Method of producing field effect transistor
 IN Saito, Naoto, Tokyo, Japan
 Aoki, Kenji, Tokyo, Japan
 Akamine, Tadao, Tokyo, Japan
 Kojima, Yoshikazu, Tokyo, Japan
 Takahashi, Kunihiro, Tokyo, Japan
 Kinbara, Masahiko, Tokyo, Japan
 PA Seiko Instruments, Inc., Tokyo, Japan (non-U.S. corporation)
 PI US 5124272 19920623
 AI US 1990-565960 19900813 (7)
 PRAI JP 1989-209287 19890811
 JP 1989-209288 19890811
 JP 1989-209289 19890811
 JP 1989-209291 19890811
 JP 1989-213192 19890818
 JP 1989-231276 19890906
 JP 1989-231277 19890906
 JP 1989-231279 19890906
 JP 1989-231280 19890906
 JP 1989-318557 19891206
 JP 1989-318558 19891206
 DT Utility
 LN.CNT 1369
 INCL INCLM: 437/041.000
 INCLS: 437/044.000; 437/045.000; 437/192.000; 437/946.000
 NCL NCLM: 438/297.000
 NCLS: 438/300.000; 438/301.000; 438/307.000
 IC [5]
 ICM: H01L021-265
 EXF 437/41; 437/40; 437/44; 437/192; 437/45; 437/913; 437/946

L2 ANSWER 24 OF 32 USPATFULL
 AN 92:41010 USPATFULL
 TI Step-cut insulated gate static induction transistors and method of
 manufacturing the same
 IN Nishizawa, Junichi, Sendai, Japan
 Takeda, Nobuo, Sendai, Japan

PA Suzuki, Sohbe, Sendai, Japan
 Research Development Corporation of Japan, Tokyo, Japan (non-U.S. corporation)
 PI US 5115287 19920519
 AI US 1991-752934 19910830 (7)
 RLI Continuation of Ser. No. US 1990-527677, filed on 23 May 1990, now abandoned which is a continuation of Ser. No. US 1987-122720, filed on 18 Nov 1987, now abandoned
 PRAI JP 1986-273934 19861119
 JP 1986-273935 19861119
 JP 1986-276754 19861121
 JP 1986-276755 19861121
 DT Utility
 LN.CNT 897
 INCL INCLM: 357/023.400
 INCLS: 357/023.120; 357/041.000; 357/055.000
 NCL NCLM: 257/334.000
 NCLS: 257/332.000
 IC [5]
 ICM: H01L029-10
 ICS: H01L029-78; H01L029-06
 EXF 357/23.4; 357/55; 357/23.12; 357/41

L2 ANSWER 25 OF 32 USPATFULL
 AN 92:7155 USPATFULL
 TI Process for preparing a thin film of superconducting compound oxide
 IN Harada, Keizo, Hyogo, Japan
 Fujimori, Naoji, Hyogo, Japan
 Yazu, Shuji, Hyogo, Japan
 Jodai, Tetsuji, Hyogo, Japan
 PA Sumitomo Electric Industries, Ltd., Osaka, Japan (non-U.S. corporation)
 PI US 5084265 19920128
 AI US 1990-525217 19900516 (7)
 RLI Continuation of Ser. No. US 1988-235459, filed on 24 Aug 1988, now abandoned
 PRAI JP 1987-209841 19870824
 DT Utility
 LN.CNT 565
 INCL INCLM: 423/592.000
 INCLS: 075/010.110; 075/010.290; 075/010.640
 NCL NCLM: 505/473.000
 NCLS: 075/010.110; 075/010.290; 075/010.640; 423/263.000; 423/593.000; 505/480.000
 IC [5]
 ICM: C22B004-00
 EXF 075/10.13; 075/10.11; 075/10.29; 075/10.64; 423/592
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 26 OF 32 USPATFULL
 AN 91:82067 USPATFULL
 TI Controlled high rate deposition of metal oxide films
 IN Bunshah, Rointan F., Playa del Rey, CA, United States
 Deshpandey, Chandra V., Los Angeles, CA, United States
 Doerr, Hans J., Westlake Village, CA, United States
 Yoon, Jong S., Northridge, CA, United States
 PA The Regents of the University of California, Oakland, CA, United States (U.S. corporation)
 PI US 5055319 19911008
 AI US 1990-503298 19900402 (7)
 DT Utility
 LN.CNT 604
 INCL INCLM: 427/038.000
 INCLS: 427/042.000; 427/050.000; 427/255.000; 427/255.300; 427/294.000;

427/295.000; 427/314.000; 427/319.000
 NCL NCLM: 427/567.000
 NCLS: 427/294.000; 427/295.000; 427/314.000; 427/319.000; 427/576.000;
 427/587.000
 IC [5]
 ICM: B05D003-06
 EXF 427/35; 427/42; 427/38; 427/50; 427/255.3; 427/255; 427/294; 427/295;
 427/314; 427/319
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 27 OF 32 USPATFULL
 AN 91:61117 USPATFULL
 TI Insulated gate semiconductor device using compound semiconductor at the
 channel
 IN Shimbo, Masafumi, Tokyo, Japan
 PA Seiko Instruments Inc., Japan (non-U.S. corporation)
 PI US 5036374 19910730
 AI US 1988-180359 19880411 (7)
 PRAI JP 1987-87370 19870409
 DT Utility
 LN.CNT 315
 INCL INCLM: 357/023.200
 INCLS: 357/023.150; 357/016.000; 437/132.000
 NCL NCLM: 257/192.000
 NCLS: 257/289.000; 257/410.000; 438/285.000
 IC [5]
 ICM: H01L029-20
 ICS: H01L029-78; H01L029-161; H01L021-20
 EXF 357/23.2; 357/23.15; 357/16; 437/132
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 28 OF 32 USPATFULL
 AN 90:17942 USPATFULL
 TI X-ray image intensifier and method of manufacturing the same
 IN Homma, Katsuhisa, Kawasaki, Japan
 Kimura, Sakae, Tokyo, Japan
 Nikaido, Masaru, Miura, Japan
 Ouchi, Yoshiaki, Yokohama, Japan
 Obata, Yoshiharu, Ootawara, Japan
 Uemura, Yoshikazu, Ootawara, Japan
 Sato, Syozo, Sagamihara, Japan
 PA Kabushiki Kaisha Toshiba, Kawasaki, Japan (non-U.S. corporation)
 PI US 4906893 19900306
 AI US 1988-286865 19881220 (7)
 PRAI JP 1987-327512 19871225
 JP 1988-251932 19881007
 DT Utility
 LN.CNT 629
 INCL INCLM: 313/525.000
 INCLS: 313/467.000; 250/486.100; 427/064.000; 427/068.000
 NCL NCLM: 313/525.000
 NCLS: 250/486.100; 313/467.000; 427/064.000; 427/068.000; 976/DIG.439
 IC [4]
 ICM: H01J029-20
 ICS: B05D005-12
 EXF 313/525; 313/467; 313/469; 427/64; 427/68; 427/69; 250/486.1;
 252/301.6S
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 29 OF 32 USPATFULL
 AN 89:71670 USPATFULL
 TI Method of growing group III-V compound semiconductor epitaxial layer
 IN Mochizuki, Kouji, Isehara, Japan

Ozeki, Masashi, Yokohama, Japan
 Ohtsuka, Nobuyuki, Atsugi, Japan
 PA Fujitsu Limited, Kawasaki, Japan (non-U.S. corporation)
 PI US 4861417 19890829
 AI US 1988-172671 19880324 (7)
 PRAI JP 1987-71747 19870327
 DT Utility
 LN.CNT 666
 INCL INCLM: 156/610.000
 INCLS: 156/611.000; 156/613.000; 156/614.000; 156/DIG.061; 156/DIG.081;
 156/DIG.094; 156/DIG.103
 NCL NCLM: 117/089.000
 NCLS: 117/101.000; 117/104.000; 117/105.000; 117/902.000; 117/939.000;
 117/954.000
 IC [4]
 ICM: C30B025-14
 EXF 156/610; 156/611; 156/613; 156/614; 156/DIG.61; 156/DIG.81; 156/DIG.94;
 156/DIG.103; 437/236
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 30 OF 32 USPATFULL
 AN 89:69723 USPATFULL
 TI Method for epitaxial growth of compound semiconductor using MOCVD with
molecular layer epitaxy
 IN Matsumoto, Fumio, Miyagi, Japan
 PA Research Development Corporation of Japan, Junichi Nishizawa and Oki
 Electric Industry Co., Ltd., Japan (non-U.S. corporation)
 PI US 4859625 19890822
 AI US 1987-123497 19871120 (7)
 PRAI JP 1986-277829 19861122
 DT Utility
 LN.CNT 878
 INCL INCLM: 437/081.000
 INCLS: 148/DIG.025; 148/DIG.041; 148/DIG.048; 148/DIG.057; 148/DIG.072;
 148/DIG.110; 148/DIG.094; 156/613.000; 437/019.000; 437/111.000;
 437/133.000; 437/173.000; 437/936.000; 437/942.000; 437/963.000;
 427/053.100
 NCL NCLM: 117/093.000
 NCLS: 117/089.000; 117/092.000; 117/103.000; 117/953.000; 117/954.000;
 117/955.000; 117/956.000; 148/DIG.025; 148/DIG.041; 148/DIG.048;
 148/DIG.057; 148/DIG.072; 148/DIG.094; 148/DIG.110; 427/584.000;
 427/586.000; 438/935.000
 IC [4]
 ICM: H01L021-205
 EXF 148/DIG.6; 148/21; 148/25; 148/41; 148/48; 148/56; 148/65; 148/71;
 148/72; 148/94; 148/110; 148/160; 148/169; 148/57; 156/610-614;
 427/53.1; 427/54.1; 437/19; 437/81; 437/107; 437/108; 437/110; 437/111;
 437/133; 437/173; 437/936; 437/942; 437/949; 437/963
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 31 OF 32 USPATFULL
 AN 89:42995 USPATFULL
 TI Method for growing single crystal thin films of element semiconductor
 IN Nishizawa, Junichi, Sendai, Japan
 Aoki, Kenji, Matsudo, Japan
 PA Research Development Corporation of Japan, Tokyo, Japan (non-U.S.
 corporation)
 Junichi Nishizawa, Sendai, Japan (non-U.S. corporation)
 Seiko Instruments, Inc., Tokyo, Japan (non-U.S. corporation)
 PI US 4834831 19890530
 AI US 1987-93505 19870904 (7)
 PRAI JP 1986-209575 19860908
 DT Utility

LN.CNT 350
INCL INCLM: 156/611.000
INCLS: 156/610.000; 156/613.000; 156/614.000; 156/DIG.064; 156/DIG.102;
156/DIG.103
NCL NCLM: 117/093.000
NCLS: 117/935.000
IC [4]
ICM: C30B025-10
ICS: C30B025-14
EXF 156/610; 156/611; 156/613; 156/614; 156/DIG.64; 156/DIG.102;
156/DIG.103
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 32 OF 32 USPATFULL
AN 88:55290 USPATFULL
TI Preparation process of compound semiconductor
IN Kobayashi, Naoki, Iruma, Japan
Makimoto, Toshiki, Tokorozawa, Japan
Horikoshi, Yoshiji, Akishima, Japan
PA Nippon Telegraph & Telephone Corporation, Tokyo, Japan (non-U.S.
corporation)
PI US 4767494 19880830
AI US 1986-909287 19860919 (6)
PRAI JP 1986-156260 19860704
JP 1986-176611 19860729
DT Utility
LN.CNT 2116
INCL INCLM: 156/606.000
INCLS: 156/613.000; 437/110.000
NCL NCLM: 117/093.000
NCLS: 117/939.000; 117/953.000; 117/954.000; 117/955.000
IC [4]
ICM: C30B025-02
EXF 156/606; 156/610; 156/612; 156/613; 156/DIG.70; 156/DIG.89;
156/DIG.113;
148/DIG.72; 148/DIG.160; 427/51; 427/86; 437/110
CAS INDEXING IS AVAILABLE FOR THIS PATENT.